Abdesselam, M., see Chibani	50 (1991) 177	Baranovskii, S.D., Theoretical basis for	
Abstreiter, G., Micro-Raman spectrosco-		the quantitative characterization of	
py for characterization of semiconduc-		impurities in n-type III-V compound	
tor devices	50 (1991) 73	semiconductors by photoelectromag-	
Adams, P.M., see Moss	50 (1991) 337	netic spectroscopy	50 (1991) 218
Adriaenssens, G.J., see Usala	50 (1991) 265	Barba, M.F., see Fariñas	50 (1991) 202
Amarger, V., C. Dubon-Chevallier, A.C.		Barnard, W.O., see Bredell	50 (1991) 466
Papadopoulo, B. Descouts and Y. Gao,		Barnett, S.J., see Keir	50 (1991) 103
Correlated use of characterization		Barnett, S.J., see Lee	50 (1991) 428
techniques to optimize the Mg implan-		Baudet, M., see Auvray	50 (1991) 109
tation annealing for self-aligned HBT's	50 (1991) 462	Bauer, J.G., R. Treichler, T. Hillmer, J.	
Ammerlaan, C.A.J., see Heijmink Liesert	50 (1991) 245	Müller and G. Ebbinghaus, Optimiza-	
Ammerlaan, C.A.J., see Van Gisbergen	50 (1991) 273	tion of Zn dopant profiles in a pin-di-	
Anderson, F.G., see O'Connor	50 (1991) 312	ode/FET by combination of depth	
Anderson, M.A., see Woolf	50 (1991) 445	profiling techniques: a SIMS, ECV	
Anderson, T., see Deneuville	50 (1991) 308	and AES study	50 (1991) 138
Antolini, A. and C. Lamberti, Computing		Baumgartner, M. and K. Löhnert, Char-	
errors in Fourier transform photo-		acterization of si-GaAs wafer quality	
luminescence	50 (1991) 212	by room-temperature photolumines-	
Ardelean, I., see Gao	50 (1991) 131	cence	50 (1991) 222
As, D.J., see Wang	50 (1991) 228	Baurichter, A., M. Deicher, S. Deubler,	
Asakura, H., see Ohnishi	50 (1991) 233	D. Forkel, J. Meier, H. Wolf, W. Witt-	
Ashenford, D., J.H.C. Hogg, B. Lunn and		huhn and ISOLDE Collaboration, Mi-	
C.G. Scott, The relationship between		croscopical studies at cadmium impur-	
electrical and structural characteristics		ities in compound semiconductors	50 (1991) 165
of CdTe and CdMnTe layers grown		Bauser, E., see Strasser	50 (1991) 261
on InSb	50 (1991) 440	Benchiguer, T., E. Christoffel, A. Golt-	
Astles, M.G., see Keir	50 (1991) 103	zené, B. Mari, B. Meyer and C.	
Auret, F.D., see Bredell	50 (1991) 466	Schwab, Donor-acceptor charge	
Austin, R.F., see Donegan	50 (1991) 321	transfers in bulk semi-insulating GaAs	
Auvray, P., A. Poudoulec, M. Baudet, B.	, , ,	as revealed by photo-EPR	50 (1991) 277
Guenais, A. Regreny, C. d'Anter-		Bender, G., see Herres	50 (1991) 97
roches and J. Massies, Interface		Benyattou, T., see Roura	50 (1991) 496
roughness of GaAs/AlAs super-		Besland, M.P., see Tardy	50 (1991) 383
lattices MBE-grown on vicinal surfaces	50 (1991) 109	Besson, M., see Strasser	50 (1991) 261
Ayyub, P., see Deneuville	50 (1991) 308	Biglari, B., see Hage-Ali	50 (1991) 377
		Blunt, R., see Pickering	50 (1991) 346
Bairamov, B.H., V.A. Voitenko, I.P.		Bonnet, A., see Morsli	50 (1991) 500
Ipatova, V.V. Toporov, G. Irmer, J.		Bosacchi, A., see Ghezzi	50 (1991) 400
Monecke and E. Jahne, Characteriza-		Bosacchi, A., see Baraldi	50 (1991) 405
tion of III-V compounds by quasi-		Boudart, B., B. Prévot and C. Schwab,	()
elastic electronic scattering of light	50 (1991) 300	Free-carrier concentration in n-doped	
Baraldi, A., C. Ghezzi, A. Parisini, A.	()	InP crystals determined by Raman	
Bosacchi and S. Franchi, Analysis of		scattering measurements	50 (1991) 295
electron mobility versus temperature		Bowman, Jr., R.C., see Moss	50 (1991) 337
after photoexcitation in Si-doped		Brandstättner, M., see Sartorius	50 (1991) 369
Al <sub>x</sub> Ga <sub>1-x</sub> As	50 (1991) 405	Brec, R., see Morsli	50 (1991) 500
-x1-x. w	(****) 100	,,	30 (2772) 300

Abdesselam, M., see Chibani	50 (1991) 177	Baranovskii, S.D., Theoretical basis for	
Abstreiter, G., Micro-Raman spectrosco-		the quantitative characterization of	
py for characterization of semiconduc-		impurities in n-type III-V compound	
tor devices	50 (1991) 73	semiconductors by photoelectromag-	
Adams, P.M., see Moss	50 (1991) 337	netic spectroscopy	50 (1991) 218
Adriaenssens, G.J., see Usala	50 (1991) 265	Barba, M.F., see Fariñas	50 (1991) 202
Amarger, V., C. Dubon-Chevallier, A.C.		Barnard, W.O., see Bredell	50 (1991) 466
Papadopoulo, B. Descouts and Y. Gao,		Barnett, S.J., see Keir	50 (1991) 103
Correlated use of characterization		Barnett, S.J., see Lee	50 (1991) 428
techniques to optimize the Mg implan-		Baudet, M., see Auvray	50 (1991) 109
tation annealing for self-aligned HBT's	50 (1991) 462	Bauer, J.G., R. Treichler, T. Hillmer, J.	
Ammerlaan, C.A.J., see Heijmink Liesert	50 (1991) 245	Müller and G. Ebbinghaus, Optimiza-	
Ammerlaan, C.A.J., see Van Gisbergen	50 (1991) 273	tion of Zn dopant profiles in a pin-di-	
Anderson, F.G., see O'Connor	50 (1991) 312	ode/FET by combination of depth	
Anderson, M.A., see Woolf	50 (1991) 445	profiling techniques: a SIMS, ECV	
Anderson, T., see Deneuville	50 (1991) 308	and AES study	50 (1991) 138
Antolini, A. and C. Lamberti, Computing		Baumgartner, M. and K. Löhnert, Char-	
errors in Fourier transform photo-		acterization of si-GaAs wafer quality	
luminescence	50 (1991) 212	by room-temperature photolumines-	
Ardelean, I., see Gao	50 (1991) 131	cence	50 (1991) 222
As, D.J., see Wang	50 (1991) 228	Baurichter, A., M. Deicher, S. Deubler,	
Asakura, H., see Ohnishi	50 (1991) 233	D. Forkel, J. Meier, H. Wolf, W. Witt-	
Ashenford, D., J.H.C. Hogg, B. Lunn and		huhn and ISOLDE Collaboration, Mi-	
C.G. Scott, The relationship between		croscopical studies at cadmium impur-	
electrical and structural characteristics		ities in compound semiconductors	50 (1991) 165
of CdTe and CdMnTe layers grown		Bauser, E., see Strasser	50 (1991) 261
on InSb	50 (1991) 440	Benchiguer, T., E. Christoffel, A. Golt-	
Astles, M.G., see Keir	50 (1991) 103	zené, B. Mari, B. Meyer and C.	
Auret, F.D., see Bredell	50 (1991) 466	Schwab, Donor-acceptor charge	
Austin, R.F., see Donegan	50 (1991) 321	transfers in bulk semi-insulating GaAs	
Auvray, P., A. Poudoulec, M. Baudet, B.	, , ,	as revealed by photo-EPR	50 (1991) 277
Guenais, A. Regreny, C. d'Anter-		Bender, G., see Herres	50 (1991) 97
roches and J. Massies, Interface		Benyattou, T., see Roura	50 (1991) 496
roughness of GaAs/AlAs super-		Besland, M.P., see Tardy	50 (1991) 383
lattices MBE-grown on vicinal surfaces	50 (1991) 109	Besson, M., see Strasser	50 (1991) 261
Ayyub, P., see Deneuville	50 (1991) 308	Biglari, B., see Hage-Ali	50 (1991) 377
		Blunt, R., see Pickering	50 (1991) 346
Bairamov, B.H., V.A. Voitenko, I.P.		Bonnet, A., see Morsli	50 (1991) 500
Ipatova, V.V. Toporov, G. Irmer, J.		Bosacchi, A., see Ghezzi	50 (1991) 400
Monecke and E. Jahne, Characteriza-		Bosacchi, A., see Baraldi	50 (1991) 405
tion of III-V compounds by quasi-		Boudart, B., B. Prévot and C. Schwab,	()
elastic electronic scattering of light	50 (1991) 300	Free-carrier concentration in n-doped	
Baraldi, A., C. Ghezzi, A. Parisini, A.	()	InP crystals determined by Raman	
Bosacchi and S. Franchi, Analysis of		scattering measurements	50 (1991) 295
electron mobility versus temperature		Bowman, Jr., R.C., see Moss	50 (1991) 337
after photoexcitation in Si-doped		Brandstättner, M., see Sartorius	50 (1991) 369
Al <sub>x</sub> Ga <sub>1-x</sub> As	50 (1991) 405	Brec, R., see Morsli	50 (1991) 500
-x1-x. w	(****) 100	,,	30 (2772) 300

Bredell, L.J., F.D. Auret, G. Myburg and		De Potter, M., see Frigeri	50 (1991) 115
W.O. Barnard, Electrical characteriza-	50 (1001) 455	Deicher, M., see Pfeiffer	50 (1991) 154
tion of argon-ion sputtered n-GaAs	50 (1991) 466	Deicher, M., see Magerle	50 (1991) 159
Breivik, L., see Brozel	50 (1991) 475	Deicher, M., see Baurichter	50 (1991) 163
Bremond, G., see Hizem	50 (1991) 490	Deneuville, A., D.B. Tanner, R.M. Park	
Bremond, G., see Roura	50 (1991) 496	and P.H. Holloway, Semiconductor	
Brozel, M.R., see Tüzemen	50 (1991) 395	electrical properties from the frequen-	
Brozel, M.R., L. Breivik, D.J. Stirland,		cy dependence of the dielectric con-	
G.M. Williams and A.G. Cullis, Dislo-		stant: application to n-type ZnSe het-	50 (1001) 20
cation density, infrared absorption and		eroepitaxial thin films	50 (1991) 28:
cathodoluminescence mapping of mi-		Deneuville, A., C.H. Park, P. Ayyub, T.	
crostructure associated with disloca- tion cells in semi-insulating LEC GaAs	50 (1991) 475	Anderson, P. Lowen, K. Jones and P.H. Holloway, O implantation in	
Burkhard, H., see Dinges	50 (1991) 359	ZnSe: lattice distortion by Raman	
burkhard, H., see Dinges	30 (1991) 339	measurement	50 (1991) 30
		Derekis, A., see Dimoulas	50 (1991) 353
Caillard, D., see Levade	50 (1991) 119	Descouts, B., see Amarger	50 (1991) 462
Callec, R., see L'Haridon	50 (1991) 237	Desnica, D.I., B. Šantić and U.V. Des-	30 (1991) 40
Carles, R., see Raisin	50 (1991) 434	nica, Time-evolution of low-tempera-	
Castaldini, A., A. Cavallini, E. Gombia,		ture photoconductivity and Hall mo-	
R. Mosca and L. Tarricone, Evalua-		bility in semi-insulating GaAs	50 (1991) 269
tion of the diffusion length of minor-		Desnica, U., see Magerle	50 (1991) 159
ity carriers in bulk GaAs	50 (1991) 485	Desnica, U.V., see Desnica	50 (1991) 269
Cavallini, A., see Castaldini	50 (1991) 485	Deubler, S., see Baurichter	50 (1991) 165
Cerva, H., Transmission electron mi-		Deveaud, B., Subpicosecond lumines-	30 (1991) 10.
croscopy of heteroepitaxial layer		cence spectroscopy of heterostructures	
structures	50 (1991) 19	(Extended Abstract)	50 (1991) 63
Cerva, H., see Schwarz	50 (1991) 456	Dimoulas, A., A. Derekis, G. Kyriakidis	30 (1991) 03
Cetronio, A., see Nipoti	50 (1991) 410	and A. Christou, Alloy disorder ef-	
Chen, B.L., M. Eckstein and HU.		fects in III-V ternaries studied by	
Habermeier, Cathodoluminescence in-		modulation spectroscopy	50 (1991) 353
vestigations of RIE-induced defects in		Dinges, H.W., B. Kempf, H. Burkhard	30 (1771) 333
InP	50 (1991) 191	and R. Göbel, Determination of ion	
Chevy, A., see Mari	50 (1991) 415	beam etching damage on InP by spec-	
Chibani, H., J.P. Stoquert, M. Hage-Ali,		troscopic ellipsometry	50 (1991) 359
J.M. Koebel, M. Abdesselam and P.		Donegan, J.F., J.P. Doran, R.P. Stanley,	30 (1))1) 33)
Siffert, Carbon analysis in CdTe by		J. Hegarty, R.D. Feldman and R.F.	
nuclear activation	50 (1991) 177	Austin, Resonant Rayleigh scattering	
Cho, G.C., see Kütt	50 (1991) 325	from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe	
Christoffel, E., see Benchiguer	50 (1991) 277	quantum wells: measurement of ho-	
Christou, A., see Dimoulas	50 (1991) 353	mogeneous linewidths	50 (1991) 321
Conan, A., see Morsli	50 (1991) 500	Doran, J.P., see Donegan	50 (1991) 321
Coquille, R., see L'Haridon	50 (1991) 237	Dubois, S., see Strasser	50 (1991) 261
Couderc, J.J., see Levade	50 (1991) 119	Dubon-Chevallier, C., see Amarger	50 (1991) 462
Couret, A., see Levade	50 (1991) 119		() 102
Crean, G.M., P.A.F. Herbert, I. Little,		Filliant C. and Barre	60 (1001) 139
W.M. Kelly, J.Y. Marzin, A. Izrael		Ebbinghaus, G., see Bauer	50 (1991) 138
and B. Jusserand, Investigation of re-		Eckstein, M., see Chen	50 (1991) 191
active ion etch-induced damage in InP		Emanuelsson, P., see Meyer	50 (1991) 420
surfaces using a noncontact photo-	50 (1001) 501	Endrédi, G., see Horányi	50 (1991) 143
thermal radiometric probe	50 (1991) 281		
Cullis, A.G., see Brozel	50 (1991) 475	Fariñas, J.C. and M.F. Barba, Inductively	
		coupled plasma-atomic emission	
D'Anterroches, C., see Auvray	50 (1991) 109	spectrometry (ICP-AES): an analyti-	
De las Heras, C., I.J. Ferrer and C.		cal technique for the chemical char-	
Sánchez, Comparison of pyrite thin		acterization of perovskite ceramic	
films obtained from Fe and natural		semiconductors	50 (1991) 202
	50 (1991) 505	Favennec, P.N., see L'Haridon	50 (1991) 237

Feldman, R.D., see Donegan	50 (1991) 321	Grimmeiss, H.G. and M. Kleverman,	
Ferrer, I.J., see De las Heras	50 (1991) 505	Electrical and optical defect spec-	
Fewster, P.F., Multicrystal X-ray diffrac-		troscopy of compound semiconduc-	
tion of heteroepitaxial structures	50 (1991) 9	tors	50 (1991) 52
Fischer, T., see Schwarz	50 (1991) 456	Grovenor, C.R.M., see Mackenzie	50 (1991) 196
Forkel, D., see Pfeiffer	50 (1991) 154	Guenais, B., see Auvray	50 (1991) 109
Forkel, D., see Baurichter	50 (1991) 165	Guillot, G., see Hizem	50 (1991) 490
Fornari, R., N. Tchandjou, P. Gall and		Guillot, G., see Roura	50 (1991) 496
J.M. Lussert, A study of structural		Gumienny, Z., see Jezierski	50 (1991) 341
properties of bulk double-doped InP		Gusinsky, G.M., see Kudoyarova	50 (1991) 173
by laser scattering tomography and		Gustafsson, A., S. Nilsson and L. Samuel-	
photoetching	50 (1991) 207	son, Intensity variations in the near-	
Foxon, C.T., Control of MBE, MOMBE		band-edge recombination of GaP epi-	
and CBE growth using RHEED	50 (1991) 28	taxial layers, grown on (111) and (001)	
Franchi, S., see Ghezzi	50 (1991) 400	oriented substrates, as observed by	
Franchi, S., see Baraldi	50 (1991) 405	cathodoluminescence imaging	50 (1991) 186
Frigeri, C., J.L. Weyher and M. De Potter,			
TEM study of the origin of the surface		Habermeier, HU., see Chen	50 (1991) 191
microroughness in DSL photoetched	the American Control	Hage-Ali, M., see Chibani	50 (1991) 177
Si-implanted GaAs wafers	50 (1991) 115	Hage-Ali, M., B. Yaacoub, S. Mergui, M.	30 (1771) 177
		Samimi, B. Biglari and P. Siffert, Mi-	
Gall, P., see Fornari	50 (1991) 207	croscopic defect level characterization	
Gall, P., see L'Haridon	50 (1991) 237	of semi-insulating compound semicon-	
Gao, Y., I. Ardelean, D. Renard, B. Rose	30 (1991) 237	ductors by TSC and PICTS. Applica-	
and Y. Jin, High-depth-resolution		tion to the effect of hydrogen in CdTe	50 (1991) 377
SIMS analysis for InGaAs/InP inter-		Hanesch, P., see Schwarz	50 (1991) 456
faces	50 (1991) 131	Hegarty, J., see Donegan	50 (1991) 321
Gao, Y., see Amarger	50 (1991) 462	Heijmink Liesert, B.J., M. Godlewski, T.	30 (1991) 321
Garawal, N.S., see Pickering	50 (1991) 346	Gregorkiewicz and C.A.J. Ammerlaan,	
Gauneau, M., see L'Haridon	50 (1991) 237	Neutron transmutation doping of	
Gavand, M., see Hizem	50 (1991) 490	GaP: optical studies	50 (1991) 245
Geiler, H.D., see Wagner	50 (1991) 373	Henry, M.O., see O'Connor	50 (1991) 312
Gendry, M., see Wagner	50 (1991) 383	Herbert, P.A.F., see Crean	50 (1991) 281
Ghezzi, C., R. Mosca, A. Bosacchi, S.	30 (1991) 303	Hergert, W., see Schreiber	50 (1991) 181
Franchi and E. Gombia, The influence		Herres, N., G. Bender and G. Neumann,	30 (1991) 161
of the DX center on the capacitance		Assessment of mismatched epitaxial	
of Schottky barriers in n-type AlGaAs	50 (1991) 400	layers by X-ray rocking curve mea-	
Ghezzi, C., see Baraldi	50 (1991) 405	surements and simulations	50 (1991) 97
Giess, J., see Keir	50 (1991) 103	Herzog, HJ., see Holländer	50 (1991) 450
Glynn, T.J., see O'Connor	50 (1991) 312	Hettwer, HG., W. Lerch, B. Lentfort,	30 (1331) 430
Göbel, H., see Zaus	50 (1991) 92	N.A. Stolwijk and H. Mehrer, Com-	
Göbel, R., see Dinges	50 (1991) 359	bined application of spreading-resis-	
Godlewski, M., see Heijmink Liesert	50 (1991) 245	tance and electron-microprobe depth	
Godlewski, M., see Zakrzewski	50 (1991) 257	profiling on GaAs:Zn and Si:P	50 (1991) 470
Godlewski, M., see Van Gisbergen	50 (1991) 273	Hildebrandt, S., see Schreiber	50 (1991) 181
Goltzené, A., see Benchiguer	50 (1991) 277	Hillmer, T., see Bauer	50 (1991) 138
Gombia, E., see Ghezzi	50 (1991) 400	Hizem, N., G. Bremond, L. Mayet, M.	30 (1991) 136
Gombia, E., see Castaldini		Gavand, J. Gregoire, G. Guillot and	
Gornik, E., see Castaidini Gornik, E., see Strasser	50 (1991) 485	W. Ulrici, Identification of the double	
Grattepain, C. and A.M. Huber, Sec-	50 (1991) 261		
•		and single acceptor state of isolated	50 (1991) 490
ondary ion mass spectrometry of		Ni <sub>Ga</sub> in GaAs	, ,
dopants and impurities in compound		Hofmann, D., see Mosel	50 (1991) 364
semiconductors: depth profiling of homo- and heterostructure	50 (1991) 42	Hofsäss, H., see Jahn Hogg, J.H.C., D. Shaw and D.M. Staudte,	50 (1991) 169
Gregoire, J., see Hizem	50 (1991) 42	Modelling interdiffusion in epitaxial	
Gregorkiewicz, T., see Heijmink Liesert	50 (1991) 245		
Gregorkiewicz, T., see Pleijillink Liesert Gregorkiewicz, T., see Van Gisbergen	50 (1991) 273	multilayer structures using X-ray simulation techniques	50 (1991) 87
Oregorkiewicz, 1., see van Oisbergen	30 (1991) 2/3	simulation techniques	50 (1991) 67

Hogg, J.H.C., see Ashenford	50 (1991) 440	Keller, R., see Pfeiffer	50 (1991) 154
Holländer, B., S. Mantl, B. Stritzker, F.		Keller, R., see Magerle	50 (1991) 159
Schäffler, HJ. Herzog and E. Kasper,		Kelly, W.M., see Crean	50 (1991) 281
Strain and defect densities in Si/		Kempf, B., see Dinges	50 (1991) 359
Si <sub>1-x</sub> Ge <sub>x</sub> heterostructures investigated		Kleverman, M., see Grimmeiss	50 (1991) 52
by ion scattering and X-ray diffrac-		Knudsen, J.F., see Moss	50 (1991) 337
tion	50 (1991) 450	Koebel, J.M., see Chibani	50 (1991) 177
Holloway, P.H., see Deneuville	50 (1991) 285	Kolodzey, J., see Schwarz	50 (1991) 456
Holloway, P.H., see Deneuville	50 (1991) 308	Kozanecki, A., see Tatarkiewicz	50 (1991) 249
Horányi, T.S., P. Tüttö and G. Endrédi,		Kudoyarova, V.Kh., G.M. Gusinsky, L.A.	
Improved method for depth profiling		Rassadin and I.V. Kudryavtsev, Hy-	
of multilayer structures	50 (1991) 143	drogen depth profile measurement in	
Houlton, M.R., see Lee	50 (1991) 428	$a-Si_{1-x}C_x$ :H films by elastic recoil de-	
Huber, A.M., see Grattepain	50 (1991) 42	tection	50 (1991) 173
Hughes, G., see Roberts	50 (1991) 424	Kudryavtsev, I.V., see Kudoyarova	50 (1991) 173
Hughes, G.J., see O'Connor	50 (1991) 312	Kurz, H., see Kütt	50 (1991) 325
•		Kütt, W., G.C. Cho, M. Strahnen and H.	
Ipatova, I.P., see Bairamov	50 (1991) 300	Kurz, Electro-optic sampling of sur-	
Irmer, G., see Bairamov	50 (1991) 300	face space-charge fields on III-V	
ISOLDE Collaboration, see Baurichter	50 (1991) 165	compounds	50 (1991) 325
ISOLDE Collaboration, see Jahn	50 (1991) 169	Kyriakidis, G., see Dimoulas	50 (1991) 353
Izrael, A., see Crean	50 (1991) 281		
	()		
Jahn, S.G., H. Hofsäss, U. Wahl, S.		Lacquet, B.M., see Swart	50 (1991) 330
Winter, E. Recknagel and ISOLDE		Lamberti, C., see Antolini	50 (1991) 212
Collaboration, Structural defect re-		Lancefield, D., see Pickering	50 (1991) 346
covery in GaP after heavy ion implan-		Landa, G., see Raisin	50 (1991) 434
tation	50 (1991) 169	Lanzieri, C., see Nipoti	50 (1991) 410
Jahne, E., see Bairamov	50 (1991) 300	Lassabatere, L., see Raisin	50 (1991) 434
Jantz, W., see Wang	50 (1991) 228	Le Guillou, Y., see L'Haridon	50 (1991) 237
Jantz, W., R. Stibal, J. Windscheif and J.		Lee, D., S.J. Barnett, A.D. Pitt, M.R.	, , , , , , , , , , , , , , , , , , , ,
Wagner, Variation of material param-		Houlton and G.W. Smith, Characteri-	
eters along the growth direction of		zation of alloy composition in	
liquid encapsulated Czochralski grown		Ga <sub>1-x</sub> Al <sub>x</sub> As/GaAs structures: com-	
GaAs ingots	50 (1991) 480	parison of photovoltage, X-ray, SIMS	
Jezierski, K., Z. Gumienny and J. Mis-		and RHEED techniques	50 (1991) 428
iewicz, Reflectometry-aided surface		Leitch, A.W.R., Th. Prescha and M.	30 (1771) 120
layer investigation	50 (1991) 341	Stutzmann, Hydrogen passivation and	
Jin, Y., see Gao	50 (1991) 131	reactivation of shallow Zn acceptors	
Jobic, S., see Morsli	50 (1991) 500	in GaAs	50 (1991) 390
Jones, K., see Deneuville	50 (1991) 308	Lentfort, B., see Hettwer	50 (1991) 470
Jusserand, B., see Crean	50 (1991) 281	Lerch, W., see Hettwer	50 (1991) 470
Jusserand, B. and F. Mollot, Confined		Levade, C., J.J. Couderc, G. Vander-	30 (1771) 410
optical vibrations: a new probe for		schaeve, D. Caillard and A. Couret,	
alloy disorder	50 (1991) 317	TEM in-situ observation of recombi-	
and discrete	()	nation-enhanced mobility of disloca-	
V-lifeli 7 con Tetaskiewicz	50 (1001) 240	tions in II–VI compounds	50 (1991) 119
Kaliński, Z., see Tatarkiewicz	50 (1991) 249	L'Haridon, H., P.N. Favennec, R. Co-	30 (1991) 119
Kalish, R., see Pfeiffer	50 (1991) 154		
Kasper, E., see Holländer	50 (1991) 450	quille, M. Salvi, M. Gauneau, Y. Le	
Kaufel, G., see Zappe	50 (1991) 290	Guillou, R. Callec and P. Gall, Spatial	
Keir, A.M., S.J. Barnett, J. Giess, T.D.		investigation of an iron-doped indium	50 (1001) 227
Walsh and M.G. Astles, A combina-		phosphide ingot	50 (1991) 237
tion of high-resolution X-ray dif-		Liddle, J.A., see Mackenzie	50 (1991) 196
fractometry and diffraction imaging		Little, I., see Crean	50 (1991) 281
techniques applied to the study of		Löhnert, K., see Baumgartner	50 (1991) 222
MOVPE-grown $Cd_xHg_{1-x}Te/CdTe$	#0 /#001:	Louis, P., see Tardy	50 (1991) 383
on GaAs	50 (1991) 103	Lowen, P., see Deneuville	50 (1991) 308

Lunn, B., see Ashenford	50 (1991) 440 50 (1991) 207	Morsli, M., A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Elec-	
Lussert, J.M., see Fornari	50 (1991) 207	tronic properties and band structure	
		of IrSe <sub>2</sub>	50 (1991) 500
		Mosca, R., see Ghezzi	50 (1991) 400
Mackenzie, R.A.D., J.A. Liddle and		Mosca, R., see Castaldini	50 (1991) 485
C.R.M. Grovenor, Ultrahigh resolu-		Mosel, F., A. Seidl, D. Hofmann and G.	00 (0772) 100
tion characterisation of compound		Müller, Infrared absorption of n- and	
semiconductors using pulsed laser		p-type Fe-doped InP and mapping of	
atom probe techniques	50 (1991) 196	the Fe distribution	50 (1991) 364
Magerle, R., see Pfeiffer	50 (1991) 154	Moss, S.C., J.F. Knudsen, R.C. Bowman,	
Magerle, R., M. Deicher, U. Desnica, R.		Jr., P.M. Adams and D.D. Smith, Pi-	
Keller, W. Pfeiffer, F. Pleiter, H.		cosecond transient photoreflectance	
Skudlik and Th. Wichert, Defects in		measurements of ion-implanted GaAs	50 (1991) 337
CdS:In detected by perturbed angular	50 (1001) 150	Müller, G., see Mosel	50 (1991) 364
correlation spectroscopy (PAC)	50 (1991) 159 50 (1991) 233	Müller, J., see Bauer	50 (1991) 138
Makita, Y., see Ohnishi	50 (1991) 450	Muschik, T., see Schwarz	50 (1991) 456
Mantl, S., see Holländer Mari, B., see Benchiguer	50 (1991) 277	Myburg, G., see Bredell	50 (1991) 466
Mari, B., A. Segura and A. Chevy, Electri-	30 (1991) 277		
cal properties of neutron-transmuta-		Nesladek, M., see Usala	50 (1991) 265
tion-doped InSe	50 (1991) 415	Neumann, G., see Herres	50 (1991) 97
Marzin, J.Y., see Crean	50 (1991) 281	Nilsson, S., see Gustafsson	50 (1991) 186
Massies, J., see Auvray	50 (1991) 109	Nipoti, R., D. Pocci, A. Cetronio and C.	( )
Matsui, J., Study of strain variation in	20 (1771) 107	Lanzieri, Carrier and mobility profile	
LEC-grown GaAs bulk crystals by		measurements in n-type ion-implanted	
synchrotron radiation X-ray topogra-		GaAs by the differential sheet resistiv-	
phy	50 (1991) 1	ity and Hall effect technique	50 (1991) 410
Matsumori, T., see Ohnishi	50 (1991) 233		
Mayet, L., see Hizem	50 (1991) 490	O'Conner CM CI MeDonach EC	
McDonagh, C.J., see O'Connor	50 (1991) 312	O'Connor, G.M., C.J. McDonagh, F.G. Anderson, T.J. Glynn, G.P. Morgan,	
McGovern, I.T., Soft X-ray photoelectron		G.J. Hughes, L. Roberts and M.O.	
spectroscopy of compound semicon-		Henry, Raman characterization of	
ductor surfaces and interfaces	50 (1991) 34	passivated GaAs surfaces	50 (1991) 312
Mehrer, H., see Hettwer	50 (1991) 470	Ohnishi, N., Y. Makita, A. Yamada, H.	30 (1331) 312
Meier, J., see Baurichter	50 (1991) 165	Asakura and T. Matsumori, Effect of	
Mendik, M., M. Ospelt, H. von Känel		substrate orientation on the defect-in-	
and P. Wachter, Determination of		duced bound exciton emissions in	
elastic properties of Si/Ge super-		GaAs grown by molecular beam epi-	
lattices and $Si_{1-x}Ge_x$ films from		taxy	50 (1991) 233
surface acoustic modes by Brillouin	** ****	Öktü, Ö., see Usala	50 (1991) 265
scattering	50 (1991) 303	Omling, P., see Meyer	50 (1991) 420
Mergui, S., see Hage-Ali	50 (1991) 377	Ospelt, M., see Mendik	50 (1991) 303
Meyer, B., see Benchiguer	50 (1991) 277	Ossart, P. and E.V.K. Rao, Investigation	
Meyer, B., P. Omling and P. Emanuels-		of surface and sub-surface defects on	
son, Landau oscillations in single		polished InP substrates using Auger	
quantum wells observed by microwave detection	50 (1991) 420	electron spectroscopy coupled to argon	
Meyerheim, H.L., see Schwarz	50 (1991) 456	ion sputtering	50 (1991) 125
Misiewicz, J., see Jezierski	50 (1991) 341		
Missous, M., see Rimmer	50 (1991) 149	Papadopoulo, A.C., see Amarger	50 (1991) 462
Mollot, F., see Jusserand	50 (1991) 317	Paprocki, K., see Tatarkiewicz	50 (1991) 249
Monecke, J., see Bairamov	50 (1991) 300	Parisini, A., see Baraldi	50 (1991) 405
Monteiro, T. and E. Pereira, Complex	30 (1771) 300	Park, C.H., see Deneuville	50 (1991) 308
formation in Mn-doped GaP samples	50 (1991) 253	Park, R.M., see Deneuville	50 (1991) 285
Morante, J.R., see Roura	50 (1991) 496	Peaker, A.R., see Rimmer	50 (1991) 149
Morgan, G.P., see O'Connor	50 (1991) 312	Pereira, E., see Monteiro	50 (1991) 253
Morgan, G.F., see O Connor			

Pfeiffer, W., M. Deicher, R. Keller, R.		Sartorius, B., M. Brandstättner and H.	
Magerle, P. Pross, H. Skudlik, Th.		Venghaus, Two-wavelength transmis-	
Wichert, H. Wolf, D. Forkel, N.		sion: a rapid and precise method for	
Moriya and R. Kalish, Characteriza-		measuring the light absorption in	
tion of Cd implanted and annealed		semiconductors	50 (1991) 369
GaAs and InP by perturbed angular		Schäffler, F., see Holländer	50 (1991) 450
correlation (PAC) spectroscopy	50 (1991) 154	Scherzer, B.M.U., see Schwarz	50 (1991) 456
Pfeiffer, W., see Magerle	50 (1991) 159	Schreiber, J., W. Hergert and S.	30 (1771) 130
Pickering, C., N.S. Garawal, D. Lance-	(1772) 107	Hildebrandt, Combined application of	
field, J.P. Piel and R. Blunt, Non-de-		SEM-CL and SEM-EBIC for the in-	
structive characterisation of (Ga,In,		vestigation of compound semiconduc-	
Al,As,P)-based ternary multilayer		tors	50 (1991) 181
structures using spectroscopic el-		Schuster, M., see Zaus	50 (1991) 92
lipsometry	50 (1991) 346	Schwab, C., see Benchiguer	50 (1991) 277
Piel, J.P., see Pickering	50 (1991) 346	Schwab, C., see Boudart	50 (1991) 295
Pitt, A.D., see Lee	50 (1991) 428	Schwarz, R., T. Fischer, P. Hanesch, T.	30 (1371) 233
Pleiter, F., see Magerle	50 (1991) 159	Muschik, J. Kolodzey, H. Cerva, H.L.	
Pocci, D., see Nipoti	50 (1991) 410	Meyerheim and B.M.U. Scherzer,	
Post, G., see Tardy	50 (1991) 383	Limitations of interface sharpness in	
Poudoulec, A., see Auvray	50 (1991) 109	a-Si:H/a-SiC:H multilayers	50 (1991) 456
Prescha, Th., see Leitch	50 (1991) 390	Scott, C.G., see Ashenford	50 (1991) 440
Prévot, B., see Boudart	50 (1991) 295	Segura, A., see Mari	50 (1991) 415
Pross, P., see Pfeiffer	50 (1991) 154	Seidl, A., see Mosel	50 (1991) 364
rioss, r., see rieniei	30 (1991) 134	Shaw, D., see Hogg	50 (1991) 87
		Siffert, P., see Chibani	50 (1991) 177
Raisin, C., A. Rocher, G. Landa, R. Carles		Siffert, P., see Hage-Ali	50 (1991) 377
and L. Lassabatere, GaSb/GaAs het-		Skudlik, H., see Pfeiffer	50 (1991) 154
eroepitaxy characterized as a stress-		Skudlik, H., see Magerle	50 (1991) 159
free system	50 (1991) 434	Smith, D.D., see Moss	50 (1991) 337
Rao, E.V.K., see Ossart	50 (1991) 125	Smith, G.W., see Lee	50 (1991) 428
Rassadin, L.A., see Kudoyarova	50 (1991) 173	Stanley, R.P., see Donegan	50 (1991) 321
Recknagel, E., see Jahn	50 (1991) 169	Staudte, D.M., see Hogg	50 (1991) 87
Regreny, A., see Auvray	50 (1991) 109	Stibal, R., see Jantz	50 (1991) 480
Reithmaier, JP., see Zaus	50 (1991) 92	Stirland, D.J., see Brozel	50 (1991) 475
Renard, D., see Gao	50 (1991) 131	Stolwijk, N.A., see Hettwer	50 (1991) 470
Riechert, H., see Strasser	50 (1991) 261	Stoquert, J.P., see Chibani	50 (1991) 177
Rimmer, J.S., M. Missous and A.R.	00 (1271) 201	Stradling, R.A., Far-infrared spectroscopy	30 (1991) 177
Peaker, A new, fast method for the		of impurities in semiconductors	50 (1991) 65
computer simulation of CV profiles in		Strahnen, M., see Kütt	50 (1991) 325
multilayer structures	50 (1991) 149	Strasser, G., S. Dubois, M. Besson, E.	30 (1991) 323
Roberts, L., see O'Connor	50 (1991) 312	Gornik, G. Weimann, E. Bauser and	
Roberts, L. and G. Hughes, An investiga-	()	H. Riechert, Analysis of impurity dis-	
tion of metal/GaAs(100) interfaces by		tribution in n-GaAs layers by photo-	
deep level transient spectroscopy	50 (1991) 424	conductivity and cyclotron resonance	
Rocher, A., see Raisin	50 (1991) 434	measurements	50 (1991) 261
Rose, B., see Gao	50 (1991) 131	Stritzker, B., see Holländer	50 (1991) 450
Roura, P., J.R. Morante, G. Bremond, T.	()	Stutzmann, M., see Leitch	50 (1991) 390
Benyattou, G. Guillot and W. Ulrici,		Swart, P.L., B.M. Lacquet and R. Thavar,	30 (1991) 390
Complete identification of the Ti-re-		Physical characterization of OMVPE-	
lated levels in GaP	50 (1991) 496	grown $Al_xGa_{1-x}As$ multi-layer films	
and a vent as one	. ()	by means of non-destructive optical	
		reflectometry	50 (1991) 330
Salvi, M., see L'Haridon	50 (1991) 237	reflectomeny	30 (1991) 330
Samimi, M., see Hage-Ali	50 (1991) 377		
Samuelson, L., see Gustafsson	50 (1991) 186	Tanner, D.B., see Deneuville	50 (1991) 285
Sánchez, C., see De las Heras	50 (1991) 505	Tardy, J., I. Thomas, P. Viktorovitch, M.	
Šantić, B., see Desnica	50 (1991) 269	Gendry, J.L. Perrossier, C. Santinelli,	
Santinelli, C., see Tardy	50 (1991) 383	M.P. Besland, P. Louis and G. Post,	
	,		

Long-term stability of InP MIS de-		Wahl, U., see Jahn	50 (1991) 169
vices	50 (1991) 383	Walsh, T.D., see Keir	50 (1991) 103
Tarricone, L., see Castaldini	50 (1991) 485	Wang, Z.M., J. Windscheif, D.J. As and	
Tatarkiewicz, J., A. Kozanecki, Z. Kaliń-		W. Jantz, Ambient and low tempera-	
ski and K. Paprocki, Photolumines-		ture photoluminescence topography of	
cence study of proton-implanted		GaAs substrates, epitaxial and im-	
$InP_{1-x}As_x:Yb$	50 (1991) 249	planted layers	50 (1991) 228
Tchandjou, N., see Fornari	50 (1991) 207	Weimann, G., see Strasser	50 (1991) 261
Thavar, R., see Swart	50 (1991) 330	Westwood, D.I., see Woolf	50 (1991) 445
Thomas, I., see Tardy	50 (1991) 383	Weyher, J.L., see Frigeri	50 (1991) 115
Toporov, V.V., see Bairamov	50 (1991) 300	Wichert, Th., see Pfeiffer	50 (1991) 154
Tregouet, Y., see Morsli	50 (1991) 500	Wichert, Th., see Magerle	50 (1991) 159
Treichler, R., see Bauer	50 (1991) 138	Williams, G.M., see Brozel	50 (1991) 475
Tüttö, P., see Horányi	50 (1991) 143	Williams, R.H., see Woolf	50 (1991) 445
Tüzemen, S. and M.R. Brozel, An investi-		Windscheif, J., see Wang	50 (1991) 228
gation of photo-quenching properties		Windscheif, J., see Jantz	50 (1991) 480
of LEC GaAs by using optical and		Winkler, N., see Wagner	50 (1991) 373
electrical techniques	50 (1991) 395	Winter, S., see Jahn	50 (1991) 169
•		Witthuhn, W., see Baurichter	50 (1991) 165
Ulrici, W., see Hizem	50 (1991) 490	Wolf, H., see Pfeiffer	50 (1991) 154
Ulrici, W., see Roura	50 (1991) 496	Wolf, H., see Baurichter	50 (1991) 165
Usala, S., G.J. Adriaenssens, Ö. Öktü and		Woolf, D.A., D.I. Westwood, M.A. An-	, ,
M. Nesladek, Post-transit-time analy-		derson and R.H. Williams, The molec-	
sis of time-of-flight photocurrents	50 (1991) 265	ular beam epitaxial growth of	
		$GaAs(\overline{1}\overline{1}\overline{1})/Si(111)$ : a variable growth	
Van Gisbergen, S.J.C.H.M., M. Godlew-		temperature study	50 (1991) 445
ski, T. Gregorkiewicz and C.A.J. Am-			
merlaan, Interstitial Mn as a new		Yaacoub, B., see Hage-Ali	50 (1991) 377
donor in GaP and GaAs: an EPR		Yamada, A., see Ohnishi	50 (1991) 233
study	50 (1991) 273		
Vanderschaeve, G., see Levade	50 (1991) 119	Zakrzewski, A. and M. Godlewski, Three-	
Venghaus, H., see Sartorius	50 (1991) 369	center Auger effect and the quantum	
Viktorovitch, P., see Tardy	50 (1991) 383	yield of the luminescence of ZnS-based	
Voitenko, V.A., see Bairamov	50 (1991) 300	phosphors	50 (1991) 257
Von Känel, H., see Mendik	50 (1991) 303	Zappe, H.P. and G. Kaufel, Reactive- ion-etch damage in GaAs processing	
Wachter, P., see Mendik	50 (1991) 303	evaluated by a microwave absorption	
Wagner, J., Raman spectroscopy for im-		technique	50 (1991) 290
purity characterization in III-V semi-		Zaus, R., M. Schuster, H. Göbel and JP.	
conductors	50 (1991) 79	Reithmaier, Characterization of (In,	
Wagner, J., see Jantz	50 (1991) 480	Ga)As/GaAs strained-layer multiple	
Wagner, M., N. Winkler and H.D. Geiler,		quantum wells with high-resolution	
Single-beam thermowave analysis of		X-ray diffraction and computer simu-	
Control of the contro	50 (1991) 373	January and Tomport Online	

Aluminium		GaAs substrates, epitaxial and im- planted layers	50 (1991) 228
P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE- grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films by means of non-destructive optical		H. L'Haridon, P.N. Favennec, R. Co- quille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium	
reflectometry K. Jezierski, Z. Gumienny and J. Mis-	50 (1991) 330	phosphide ingot J. Tatarkiewicz, A. Kozanecki, Z. Kaliński and K. Paprocki, Photolumines-	50 (1991) 237
iewicz, Reflectometry-aided surface layer investigation	50 (1991) 341	cence study of proton-implanted InP <sub>1-x</sub> As <sub>x</sub> :Yb  A. Deneuville, C.H. Park, P. Ayyub, T.	50 (1991) 249
Amorphous materials		Anderson, P. Lowen, K. Jones and P.H. Holloway, O implantation in	
V.Kh. Kudoyarova, G.M. Gusinsky, L.A. Rassadin and I.V. Kudryavtsev, Hy- drogen depth profile measurement in		ZnSe: lattice distortion by Raman measurement M. Wagner, N. Winkler and H.D. Geiler,	50 (1991) 308
$a-Si_{1-x}C_x$ : H films by elastic recoil detection	50 (1991) 173	Single-beam thermowave analysis of semiconductors  V. Amarger, C. Dubon-Chevallier, A.C.	50 (1991) 373
S. Usala, G.J. Adriaenssens, Ö. Öktü and M. Nesladek, Post-transit-time analy- sis of time-of-flight photocurrents	50 (1991) 265	Papadopoulo, B. Descouts and Y. Gao, Correlated use of characterization	
R. Schwarz, T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer,		techniques to optimize the Mg implan- tation annealing for self-aligned HBT's L.J. Bredell, F.D. Auret, G. Myburg and	50 (1991) 462
Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers	50 (1991) 456	W.O. Barnard, Electrical characteriza- tion of argon-ion sputtered n-GaAs	50 (1991) 466
Annealing		Auger electron spectroscopy	
W. Pfeiffer, M. Deicher, R. Keller, R. Magerle, P. Pross, H. Skudlik, Th. Wichert, H. Wolf, D. Forkel, N. Moriya and R. Kalish, Characteriza-		P. Ossart and E.V.K. Rao, Investigation of surface and sub-surface defects on polished InP substrates using Auger electron spectroscopy coupled to argon ion sputtering	50 (1991) 125
tion of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy	50 (1991) 154	J.G. Bauer, R. Treichler, T. Hillmer, J. Müller and G. Ebbinghaus, Optimiza-	, ,
S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter, E. Recknagel and ISOLDE Collabora-	30 (1991) 134	tion of Zn dopant profiles in a pin-di- ode/FET by combination of depth profiling techniques: a SIMS, ECV	
tion, Structural defect recovery in GaP after heavy ion implantation M. Baumgartner and K. Löhnert, Char-	50 (1991) 169	and AES study	50 (1991) 138
acterization of si-GaAs wafer quality by room-temperature photolumines-		Band structure	
cence  Z.M. Wang, J. Windscheif, D.J. As and  W. Jantz, Ambient and low tempera-	50 (1991) 222	M. Morsli, A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Elec- tronic properties and band structure	
ture photoluminescence topography of		of IrSe <sub>2</sub>	50 (1991) 500

Cadmium		Siffert, Carbon analysis in CdTe by nuclear activation	50 (1991) 177
W. Pfeiffer, M. Deicher, R. Keller, R. Magerle, P. Pross, H. Skudlik, Th. Wichert, H. Wolf, D. Forkel, N. Moriya and R. Kalish, Characteriza-		M. Hage-Ali, B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Microscopic defect level characterization of semi-insulating compound semicon-	
tion of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy A. Baurichter, M. Deicher, S. Deubler, D.	50 (1991) 154	ductors by TSC and PICTS. Applica- tion to the effect of hydrogen in CdTe D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics	50 (1991) 377
Forkel, J. Meier, H. Wolf, W. Witt- huhn and ISOLDE Collaboration, Mi- croscopical studies at cadmium impur-		of CdTe and CdMnTe layers grown on InSb	50 (1991) 440
ities in compound semiconductors S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter, E. Recknagel and ISOLDE Collabora-	50 (1991) 165	Carbon	
tion, Structural defect recovery in GaP after heavy ion implantation	50 (1991) 169	H. Chibani, J.P. Stoquert, M. Hage-Ali, J.M. Koebel, M. Abdesselam and P. Siffert, Carbon analysis in CdTe by	
Cadmium sulphide		nuclear activation	50 (1991) 177
I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semicon-		Ceramics	
ductor surfaces and interfaces  R. Magerle, M. Deicher, U. Desnica, R. Keller, W. Pfeiffer, F. Pleiter, H. Skudlik and Th. Wichert, Defects in	50 (1991) 34	J.C. Fariñas and M.F. Barba, Inductively coupled plasma-atomic emission spectrometry (ICP-AES): an analyti-	
CdS: In detected by perturbed angu- lar correlation spectroscopy (PAC)  R. Fornari, N. Tchandjou, P. Gall and J.M. Lussert, A study of structural	50 (1991) 159	cal technique for the chemical char- acterization of perovskite ceramic semiconductors	50 (1991) 202
properties of bulk double-doped InP by laser scattering tomography and photoetching	50 (1991) 207	Chalcogenides	
Cadmium telluride		A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequen-	
J.H.C. Hogg, D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial multilayer structures using X-ray simulation techniques	50 (1991) 87	cy dependence of the dielectric con- stant: application to n-type ZnSe het- eroepitaxial thin films  A. Deneuville, C.H. Park, P. Ayyub, T. Anderson, P. Lowen, K. Jones and	50 (1991) 285
A.M. Keir, S.J. Barnett, J. Giess, T.D. Walsh and M.G. Astles, A combina- tion of high-resolution X-ray dif-	30 (1551) 07	P.H. Holloway, O implantation in ZnSe: lattice distortion by Raman measurement	50 (1991) 308
fractometry and diffraction imaging techniques applied to the study of MOVPE-grown Cd <sub>x</sub> Hg <sub>1-x</sub> Te/CdTe on GaAs	50 (1991) 103	J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in Cd <sub>x</sub> Zn <sub>1-x</sub> Te:ZnTe	
C. Levade, J.J. Couderc, G. Vander- schaeve, D. Caillard and A. Couret, TEM in-situ observation of recombi-	()	quantum wells: measurement of ho- mogeneous linewidths  B. Mari, A. Segura and A. Chevy, Electri-	50 (1991) 321
nation-enhanced mobility of disloca- tions in II-VI compounds H. Chibani, J.P. Stoquert, M. Hage-Ali, J.M. Koebel. M. Abdesselam and P.	50 (1991) 119	cal properties of neutron-transmuta- tion-doped InSe  M. Morsli, A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Elec-	50 (1991) 415

tronic properties and band structure of $IrSe_2$	50 (1991) 500	H. L'Haridon, P.N. Favennec, R. Co- quille, M. Salvi, M. Gauneau, Y. Le	
		Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium	
Chemical vapour deposition		phosphide ingot	50 (1991) 237
C.T. Foxon, Control of MBE, MOMBE		T. Monteiro and E. Pereira, Complex for-	
and CBE growth using RHEED	50 (1991) 28	mation in Mn-doped GaP samples	50 (1991) 253
	, ,	A. Deneuville, D.B. Tanner, R.M. Park	
Cyclotron resonance studies		and P.H. Holloway, Semiconductor electrical properties from the frequen-	
		cy dependence of the dielectric con-	
G. Strasser, S. Dubois, M. Besson, E.		stant: application to n-type ZnSe het-	
Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity dis-		eroepitaxial thin films	50 (1991) 285
tribution in n-GaAs layers by photo-		B. Boudart, B. Prévot and C. Schwab, Free-carrier concentration in n-doped	
conductivity and cyclotron resonance		InP crystals determined by Raman	
measurements	50 (1991) 261	scattering measurements	50 (1991) 295
		F. Mosel, A. Seidl, D. Hofmann and G.	
Diffusion		Müller, Infrared absorption of n- and	
		p-type Fe-doped InP and mapping of the Fe distribution	50 (1991) 364
J.H.C. Hogg, D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial		B. Sartorius, M. Brandstättner and H.	30 (1991) 304
multilayer structures using X-ray		Venghaus, Two-wavelength transmis-	
simulation techniques	50 (1991) 87	sion: a rapid and precise method for	
J.G. Bauer, R. Treichler, T. Hillmer, J.	,	measuring the light absorption in	
Müller and G. Ebbinghaus, Optimiza-		semiconductors	50 (1991) 369
tion of Zn dopant profiles in a pin-di-		R. Nipoti, D. Pocci, A. Cetronio and C. Lanzieri, Carrier and mobility profile	
ode/FET by combination of depth profiling techniques: a SIMS, ECV		measurements in n-type ion-implanted	
and AES study	50 (1991) 138	GaAs by the differential sheet resistiv-	
R. Magerle, M. Deicher, U. Desnica, R.		ity and Hall effect technique	50 (1991) 410
Keller, W. Pfeiffer, F. Pleiter, H.		B. Mari, A. Segura and A. Chevy, Electri-	
Skudlik and Th. Wichert, Defects in		cal properties of neutron-transmuta- tion-doped InSe	50 (1991) 415
CdS:In detected by perturbed angular correlation spectroscopy (PAC)	50 (1991) 159	D. Ashenford, J.H.C. Hogg, B. Lunn and	30 (1331) 113
S.J.C.H.M. van Gisbergen, M. Godlewski,	30 (1331) 133	C.G. Scott, The relationship between	
T. Gregorkiewicz and C.A.J. Am-		electrical and structural characteristics	
merlaan, Interstitial Mn as a new		of CdTe and CdMnTe layers grown	50 (1001) 440
donor in GaP and GaAs: an EPR	50 (1001) 272	on InSb  A. Castaldini, A. Cavallini, E. Gombia, R.	50 (1991) 440
study	50 (1991) 273	Mosca and L. Tarricone, Evaluation	
HG. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Com-		of the diffusion length of minority car-	
bined application of spreading-resis-		riers in bulk GaAs	50 (1991) 485
tance and electron-microprobe depth		N. Hizem, G. Bremond, L. Mayet, M.	
profiling on GaAs:Zn and Si:P	50 (1991) 470	Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double	
		and single acceptor state of isolated	
Doping effects		Ni <sub>Ga</sub> in GaAs	50 (1991) 490
I Matari Study of steels vosiciles in		P. Roura, J.R. Morante, G. Bremond, T.	
J. Matsui, Study of strain variation in LEC-grown GaAs bulk crystals by		Benyattou, G. Guillot and W. Ulrici,	
synchrotron radiation X-ray topogra-		Complete identification of the Ti-re- lated levels in GaP	50 (1991) 496
phy	50 (1991) 1	rated tevels in Oaf	30 (1331) 430
C. Grattepain and A.M. Huber, Sec-		Electrical properties	
ondary ion mass spectrometry of		Liecurcus properties	
dopants and impurities in compound semiconductors: depth profiling of		H.G. Grimmeiss and M. Kleverman,	
homo- and heterostructure	50 (1991) 42	Electrical and optical defect spec-	

troscopy of compound semiconduc- tors  T.S. Horányi, P. Tüttö and G. Endrédi,	50 (1991) 52	C. Ghezzi, R. Mosca, A. Bosacchi, S. Franchi and E. Gombia, The influence of the DX center on the capacitance	
Improved method for depth profiling of multilayer structures	50 (1991) 143	of Schottky barriers in n-type AlGaAs R. Nipoti, D. Pocci, A. Cetronio and C.	50 (1991) 400
J.S. Rimmer, M. Missous and A.R. Peaker, A new, fast method for the computer simulation of CV profiles in multi-	50 (1001) 1 10	Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted GaAs by the differential sheet resistiv-	50 (1001) 410
layer structures  J. Schreiber, W. Hergert and S. Hilde- brandt, Combined application of	50 (1991) 149	ity and Hall effect technique  B. Mari, A. Segura and A. Chevy, Electrical properties of neutron-transmuta-	50 (1991) 410
SEM-CL and SEM-EBIC for the in- vestigation of compound semiconduc- tors	50 (1991) 181	tion-doped InSe L. Roberts and G. Hughes, An investiga- tion of metal/GaAs(100) interfaces by	50 (1991) 415
Z.M. Wang, J. Windscheif, D.J. As and W. Jantz, Ambient and low temperature photoluminescence topography of GaAs substrates, epitaxial and im-	30 (1991) 161	deep level transient spectroscopy  D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics	50 (1991) 424
planted layers  H. L'Haridon, P.N. Favennec, R. Co-	50 (1991) 228	of CdTe and CdMnTe layers grown on InSb	50 (1991) 440
quille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial		L.J. Bredell, F.D. Auret, G. Myburg and W.O. Barnard, Electrical characteriza-	()
investigation of an iron-doped indium phosphide ingot	50 (1991) 237	tion of argon-ion sputtered n-GaAs HG. Hettwer, W. Lerch, B. Lentfort,	50 (1991) 466
A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequen-		N.A. Stolwijk and H. Mehrer, Com- bined application of spreading-resis- tance and electron-microprobe depth	
cy dependence of the dielectric con- stant: application to n-type ZnSe het- eroepitaxial thin films	50 (1991) 285	profiling on GaAs:Zn and Si:P W. Jantz, R. Stibal, J. Windscheif and J. Wagner, Variation of material param-	50 (1991) 470
H.P. Zappe and G. Kaufel, Reactive-ion- etch damage in GaAs processing evaluated by a microwave absorption		eters along the growth direction of liquid encapsulated Czochralski grown GaAs ingots	50 (1991) 480
technique W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of sur-	50 (1991) 290	A. Castaldini, A. Cavallini, E. Gombia, R. Mosca and L. Tarricone, Evaluation of the diffusion length of minority car-	
face space-charge fields on III-V compounds M. Hage-Ali, B. Yaacoub, S. Mergui, M.	50 (1991) 325	riers in bulk GaAs  N. Hizem, G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and	50 (1991) 485
Samimi, B. Biglari and P. Siffert, Mi- croscopic defect level characterization		W. Ulrici, Identification of the double and single acceptor state of isolated	
of semi-insulating compound semicon- ductors by TSC and PICTS. Applica- tion to the effect of hydrogen in CdTe	50 (1991) 377	Ni <sub>Ga</sub> in GaAs M. Morsli, A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Elec-	50 (1991) 490
J. Tardy, I. Thomas, P. Viktorovitch, M. Gendry, J.L. Perrossier, C. Santinelli, M.P. Besland, P. Louis and G. Post, Long-term stability of InP MIS de-		tronic properties and band structure of IrSe <sub>2</sub>	50 (1991) 500
vices A.W.R. Leitch, Th. Prescha and M. Stutz-	50 (1991) 383	Electron bombardment	
mann, Hydrogen passivation and re- activation of shallow Zn acceptors in GaAs	50 (1991) 390	C. Levade, J.J. Couderc, G. Vander- schaeve, D. Caillard and A. Couret, TEM in-situ observation of recombi-	
S. Tüzemen and M.R. Brozel, An investi- gation of photo-quenching properties	20 (1771) 370	nation-enhanced mobility of disloca- tions in II-VI compounds	50 (1991) 119
of LEC GaAs by using optical and electrical techniques	50 (1991) 395	Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution	

SIMS analysis for InGaAs/InP inter- faces	50 (1991) 131	SIMS analysis for InGaAs/InP inter- faces	50 (1991) 131
	()	J. Schreiber, W. Hergert and S. Hilde-	00 (1771) 101
Electron diffraction		brandt, Combined application of SEM-CL and SEM-EBIC for the in-	
H. Cerva, Transmission electron micros-		vestigation of compound semiconduc- tors	50 (1991) 181
copy of heteroepitaxial layer struc-		A. Dimoulas, A. Derekis, G. Kyriakidis	30 (1331) 101
tures	50 (1991) 19	and A. Christou, Alloy disorder ef-	
C.T. Foxon, Control of MBE, MOMBE	50 (1001) 30	fects in III-V ternaries studied by	
and CBE growth using RHEED  J. Tardy, I. Thomas, P. Viktorovitch, M.	50 (1991) 28	modulation spectroscopy	50 (1991) 353
Gendry, J.L. Perrossier, C. Santinelli,		C. Raisin, A. Rocher, G. Landa, R. Carles and L. Lassabatere, GaSb/GaAs het-	
M.P. Besland, P. Louis and G. Post,		eroepitaxy characterized as a stress-	
Long-term stability of InP MIS de-		free system	50 (1991) 434
vices	50 (1991) 383	R. Schwarz, T. Fischer, P. Hanesch, T.	
D. Lee, S.J. Barnett, A.D. Pitt, M.R.		Muschik, J. Kolodzey, H. Cerva, H.L.	
Houlton and G.W. Smith, Characteri-		Meyerheim and B.M.U. Scherzer,	
zation of alloy composition in $Ga_{1-x}Al_xAs/GaAs$ structures: com-		Limitations of interface sharpness in	ED (1001) 45(
parison of photovoltage, X-ray, SIMS		a-Si:H/a-SiC:H multilayers  A. Castaldini, A. Cavallini, E. Gombia, R.	50 (1991) 456
and RHEED techniques	50 (1991) 428	Mosca and L. Tarricone, Evaluation	
D.A. Woolf, D.I. Westwood, M.A. Ander-		of the diffusion length of minority car-	
son and R.H. Williams, The molecular		riers in bulk GaAs	50 (1991) 485
beam epitaxial growth of GaAs(111)/		C. De las Heras, I.J. Ferrer and C.	
Si(111): a variable growth temperature	50 (1001) AAS	Sánchez, Comparison of pyrite thin	
study	50 (1991) 445	films obtained from Fe and natural	50 (1991) 505
F1		pyrite powder	30 (1991) 303
Electron microscopy		Electron spin resonance	
H. Cerva, Transmission electron micros-		CICHM Ci-b M C-4bbi	
copy of heteroepitaxial layer struc-	50 (1001) 10	S.J.C.H.M. van Gisbergen, M. Godlewski, T. Gregorkiewicz and C.A.J. Am-	
tures	50 (1991) 19	merlaan, Interstitial Mn as a new	
I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semicon-		donor in GaP and GaAs: an EPR	
ductor surfaces and interfaces	50 (1991) 34	study	50 (1991) 273
P. Auvray, A. Poudoulec, M. Baudet, B.	()	T. Benchiguer, E. Christoffel, A. Goltzené,	
Guenais, A. Regreny, C. d'Anter-		B. Mari, B. Meyer and C. Schwab,	
roches and J. Massies, Interface		Donor-acceptor charge transfers in bulk semi-insulating GaAs as revealed	
roughness of GaAs/AlAs super-	50 (1001) 100	by photo-EPR	50 (1991) 277
lattices MBE-grown on vicinal surfaces C. Frigeri, J.L. Weyher and M. De Potter,	50 (1991) 109	B. Meyer, P. Omling and P. Emanuelsson,	()
TEM study of the origin of the surface		Landau oscillations in single quantum	
microroughness in DSL photoetched		wells observed by microwave detec-	
Si-implanted GaAs wafers	50 (1991) 115	tion	50 (1991) 420
C. Levade, J.J. Couderc, G. Vander-			
schaeve, D. Caillard and A. Couret,		Ellipsometry	
TEM in-situ observation of recombi-		v · · · · · · · · · · · · · · · · · · ·	
nation-enhanced mobility of disloca-	50 (1991) 119	K. Jezierski, Z. Gumienny and J. Mis- iewicz, Reflectometry-aided surface	
tions in II-VI compounds P. Ossart and E.V.K. Rao, Investigation	30 (1991) 119	layer investigation	50 (1991) 341
of surface and sub-surface defects on		C. Pickering, N.S. Garawal, D. Lance-	30 (1331) 341
polished InP substrates using Auger		field, J.P. Piel and R. Blunt, Non-de-	
electron spectroscopy coupled to argon		structive characterisation of (Ga,In,	
ion sputtering	50 (1991) 125	Al,As,P)-based ternary multilayer	
Y. Gao, I. Ardelean, D. Renard, B. Rose		structures using spectroscopic el-	
and Y. Jin, High-depth-resolution		lipsometry	50 (1991) 346

H.W. Dinges, B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spec- troscopic ellipsometry	50 (1991) 359	<ul> <li>I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces</li> <li>C. Grattepain and A.M. Huber, Secondary ion mass spectrometry of</li> </ul>	50 (1991) 34
Etching		dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure	50 (1991) 42
R. Fornari, N. Tchandjou, P. Gall and J.M. Lussert, A study of structural properties of bulk double-doped InP		H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spec- troscopy of compound semiconduc-	
by laser scattering tomography and photoetching	50 (1991) 207	tors	50 (1991) 52
M. Baumgartner and K. Löhnert, Char- acterization of si-GaAs wafer quality	20 (2222) 201	R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors G. Abstreiter, Micro-Raman spectroscopy	50 (1991) 65
by room-temperature photolumines- cence	50 (1991) 222	for characterization of semiconductor devices	50 (1991) 73
H.P. Zappe and G. Kaufel, Reactive-ion- etch damage in GaAs processing		J. Wagner, Raman spectroscopy for im- purity characterization in III-V semi-	
evaluated by a microwave absorption technique	50 (1991) 290	conductors  R. Zaus, M. Schuster, H. Göbel and JP.	50 (1991) 79
H.W. Dinges, B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spec-	,	Reithmaier, Characterization of (In, Ga)As/GaAs strained-layer multiple quantum wells with high-resolution	
troscopic ellipsometry	50 (1991) 359	X-ray diffraction and computer simu- lations	50 (1991) 92
Field ion microscopy		N. Herres, G. Bender and G. Neumann, Assessment of mismatched epitaxial layers by X-ray rocking curve mea-	
R.A.D. Mackenzie, J.A. Liddle and C.R.M. Grovenor, Ultrahigh resolu- tion characterisation of compound semiconductors using pulsed laser atom probe techniques	50 (1991) 196	surements and simulations  A.M. Keir, S.J. Barnett, J. Giess, T.D.  Walsh and M.G. Astles, A combination of high-resolution X-ray diffractometry and diffraction imaging techniques applied to the study of	50 (1991) 97
Gallium antimonide		MOVPE-grown $Cd_xHg_{1-x}Te/CdTe$	
		on GaAs	50 (1991) 103
C. Raisin, A. Rocher, G. Landa, R. Carles and L. Lassabatere, GaSb/GaAs het- eroepitaxy characterized as a stress- free system	50 (1991) 434	P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anterroches and J. Massies, Interface roughness of GaAs/AlAs super-	
	20 (2322) 101	lattices MBE-grown on vicinal surfaces	50 (1991) 109
Gallium arsenide		C. Frigeri, J.L. Weyher and M. De Potter, TEM study of the origin of the surface microroughness in DSL photoetched	
J. Matsui, Study of strain variation in LEC-grown GaAs bulk crystals by synchrotron radiation X-ray topogra-		Si-implanted GaAs wafers T.S. Horányi, P. Tüttö and G. Endrédi, Improved method for depth profiling	50 (1991) 115
phy	50 (1991) 1	of multilayer structures	50 (1991) 143
P.F. Fewster, Multicrystal X-ray diffrac- tion of heteroepitaxial structures	50 (1991) 9	J.S. Rimmer, M. Missous and A.R. Peaker, A new, fast method for the computer	
H. Cerva, Transmission electron mi- croscopy of heteroepitaxial layer		simulation of CV profiles in multi- layer structures	50 (1991) 149
structures C.T. Foxon, Control of MBE, MOMBE	50 (1991) 19	W. Pfeiffer, M. Deicher, R. Keller, R. Magerle, P. Pross, H. Skudlik, Th.	
and CBE growth using RHEED	50 (1991) 28	Wichert, H. Wolf, D. Forkel, N.	

Moriya and R. Kalish, Characteriza-		tion of III-V compounds by quasi-	
tion of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy	50 (1991) 154	elastic electronic scattering of light G.M. O'Connor, C.J. McDonagh, F.G. Anderson, T.J. Glynn, G.P. Morgan,	50 (1991) 300
A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Witt-	30 (1991) 134	G.J. Hughes, L. Roberts and M.O. Henry, Raman characterization of	
huhn and ISOLDE Collaboration, Mi- croscopical studies at cadmium impur-		passivated GaAs surfaces B. Jusserand and F. Mollot, Confined	50 (1991) 312
ities in compound semiconductors  J. Schreiber, W. Hergert and S. Hilde- brandt, Combined application of	50 (1991) 165	optical vibrations: a new probe for alloy disorder W. Kütt, G.C. Cho, M. Strahnen and H.	50 (1991) 317
SEM-CL and SEM-EBIC for the in- vestigation of compound semiconduc-		Kurz, Electro-optic sampling of surface space-charge fields on III-V	
tors	50 (1991) 181	compounds	50 (1991) 325
M. Baumgartner and K. Löhnert, Char- acterization of si-GaAs wafer quality by room-temperature photolumines-		P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE- grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films	
cence	50 (1991) 222	by means of non-destructive optical	
Z.M. Wang, J. Windscheif, D.J. As and		reflectometry	50 (1991) 330
W. Jantz, Ambient and low tempera- ture photoluminescence topography of GaAs substrates, epitaxial and im-		S.C. Moss, J.F. Knudsen, R.C. Bowman, Jr., P.M. Adams and D.D. Smith, Pi- cosecond transient photoreflectance	
planted layers  N. Ohnishi, Y. Makita, A. Yamada, H.	50 (1991) 228	measurements of ion-implanted GaAs K. Jezierski, Z. Gumienny and J. Mis-	50 (1991) 337
Asakura and T. Matsumori, Effect of substrate orientation on the defect-in-		iewicz, Reflectometry-aided surface layer investigation	50 (1991) 341
duced bound exciton emissions in GaAs grown by molecular beam epi-		C. Pickering, N.S. Garawal, D. Lance- field, J.P. Piel and R. Blunt, Non-de-	
taxy	50 (1991) 233	structive characterisation of (Ga,In,	
G. Strasser, S. Dubois, M. Besson, E. Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity dis-		Al,As,P)-based ternary multilayer structures using spectroscopic el- lipsometry	50 (1991) 346
tribution in n-GaAs layers by photo- conductivity and cyclotron resonance		A. Dimoulas, A. Derekis, G. Kyriakidis and A. Christou, Alloy disorder ef-	30 (1991) 340
measurements	50 (1991) 261	fects in III-V ternaries studied by	
D.I. Desnica, B. Šantić and U.V. Desnica,		modulation spectroscopy	50 (1991) 353
Time-evolution of low-temperature photoconductivity and Hall mobility		B. Sartorius, M. Brandstättner and H. Venghaus, Two-wavelength transmis-	
in semi-insulating GaAs S.J.C.H.M. van Gisbergen, M. Godlewski,	50 (1991) 269	sion: a rapid and precise method for measuring the light absorption in	
T. Gregorkiewicz and C.A.J. Am-		semiconductors	50 (1991) 369
merlaan, Interstitial Mn as a new		M. Wagner, N. Winkler and H.D. Geiler,	
donor in GaP and GaAs: an EPR study	50 (1991) 273	Single-beam thermowave analysis of semiconductors	50 (1991) 373
T. Benchiguer, E. Christoffel, A. Goltzené,	30 (1991) 273	A.W.R. Leitch, Th. Prescha and M. Stutz-	30 (1991) 373
B. Mari, B. Meyer and C. Schwab,		mann, Hydrogen passivation and re-	
Donor-acceptor charge transfers in		activation of shallow Zn acceptors in	
bulk semi-insulating GaAs as revealed	60 (1001) 277	GaAs	50 (1991) 390
by photo-EPR H.P. Zappe and G. Kaufel, Reactive-ion-	50 (1991) 277	S. Tüzemen and M.R. Brozel, An investi- gation of photo-quenching properties	
etch damage in GaAs processing		of LEC GaAs by using optical and	
evaluated by a microwave absorption		electrical techniques	50 (1991) 395
technique	50 (1991) 290	C. Ghezzi, R. Mosca, A. Bosacchi, S. Franchi and E. Gombia, The influence	
B.H. Bairamov, V.A. Voitenko, I.P. Ipatova, V.V. Toporov, G. Irmer, J.		of the DX center on the capacitance	
Monecke and E. Jahne, Characteriza-		of Schottky barriers in n-type AlGaAs	50 (1991) 400

A. Baraldi, C. Ghezzi, A. Parisini, A.		of the diffusion length of minority car- riers in bulk GaAs	50 (1991) 485
Bosacchi and S. Franchi, Analysis of electron mobility versus temperature after photoexcitation in Si-doped		N. Hizem, G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and	30 (1991) 483
$Al_xGa_{1-x}As$	50 (1991) 405	W. Ulrici, Identification of the double	
R. Nipoti, D. Pocci, A. Cetronio and C. Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted		and single acceptor state of isolated $Ni_{Ga}$ in $GaAs$	50 (1991) 490
GaAs by the differential sheet resistiv- ity and Hall effect technique	50 (1991) 410	Gallium phosphide	
B. Meyer, P. Omling and P. Emanuelsson,	30 (1991) 410	• •	
Landau oscillations in single quantum		I.T. McGovern, Soft X-ray photoelectron	
wells observed by microwave detec-		spectroscopy of compound semicon-	
tion	50 (1991) 420	ductor surfaces and interfaces	50 (1991) 34
L. Roberts and G. Hughes, An investiga-		A. Baurichter, M. Deicher, S. Deubler, D.	
tion of metal/GaAs(100) interfaces by deep level transient spectroscopy	50 (1991) 424	Forkel, J. Meier, H. Wolf, W. Witt- huhn and ISOLDE Collaboration, Mi-	
D. Lee, S.J. Barnett, A.D. Pitt, M.R.	30 (1))1) 424	croscopical studies at cadmium impur-	
Houlton and G.W. Smith, Characteri-		ities in compound semiconductors	50 (1991) 165
zation of alloy composition in		S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter,	
Ga <sub>1-x</sub> Al <sub>x</sub> As/GaAs structures: com-		E. Recknagel and ISOLDE Collabora-	
parison of photovoltage, X-ray, SIMS		tion, Structural defect recovery in GaP	50 (1001) 150
and RHEED techniques	50 (1991) 428	after heavy ion implantation	50 (1991) 169
C. Raisin, A. Rocher, G. Landa, R. Carles and L. Lassabatere, GaSb/GaAs het-		A. Gustafsson, S. Nilsson and L. Samuel- son, Intensity variations in the near-	
eroepitaxy characterized as a stress-		band-edge recombination of GaP epi-	
free system	50 (1991) 434	taxial layers, grown on (111) and (001)	
D.A. Woolf, D.I. Westwood, M.A. Ander-		oriented substrates, as observed by	
son and R.H. Williams, The molecular		cathodoluminescence imaging	50 (1991) 186
beam epitaxial growth of GaAs(111)/		B.J. Heijmink Liesert, M. Godlewski, T.	
Si(111): a variable growth temperature	50 (1001) 445	Gregorkiewicz and C.A.J. Ammerlaan,	
v. Amarger, C. Dubon-Chevallier, A.C.	50 (1991) 445	Neutron transmutation doping of GaP: optical studies	50 (1991) 245
Papadopoulo, B. Descouts and Y. Gao,		T. Monteiro and E. Pereira, Complex for-	30 (1371) 243
Correlated use of characterization		mation in Mn-doped GaP samples	50 (1991) 253
techniques to optimize the Mg implan-		S.J.C.H.M. van Gisbergen, M. Godlewski,	, , ,
tation annealing for self-aligned HBT's	50 (1991) 462	T. Gregorkiewicz and C.A.J. Am-	
L.J. Bredell, F.D. Auret, G. Myburg and		merlaan, Interstitial Mn as a new	
W.O. Barnard, Electrical characteriza-	60 (1001) 466	donor in GaP and GaAs: an EPR study	50 (1001) 272
tion of argon-ion sputtered n-GaAs HG. Hettwer, W. Lerch, B. Lentfort,	50 (1991) 466	P. Roura, J.R. Morante, G. Bremond, T.	50 (1991) 273
N.A. Stolwijk and H. Mehrer, Com-		Benyattou, G. Guillot and W. Ulrici,	
bined application of spreading-resis-		Complete identification of the Ti-re-	
tance and electron-microprobe depth		lated levels in GaP	50 (1991) 496
profiling on GaAs:Zn and Si:P	50 (1991) 470		
M.R. Brozel, L. Breivik, D.J. Stirland,		Germanium	
G.M. Williams and A.G. Cullis, Dislo- cation density, infrared absorption and			
cathodoluminescence mapping of mi-		P.F. Fewster, Multicrystal X-ray diffrac-	
crostructure associated with disloca-		tion of heteroepitaxial structures	50 (1991) 9
tion cells in semi-insulating LEC GaAs	50 (1991) 475	H.G. Grimmeiss and M. Kleverman,	
W. Jantz, R. Stibal, J. Windscheif and J.		Electrical and optical defect spec-	
Wagner, Variation of material param-		troscopy of compound semiconduc-	M2 2-M
eters along the growth direction of		tors	50 (1991) 52
liquid encapsulated Czochralski grown	60 (1001) 490	B.J. Heijmink Liesert, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan,	
GaAs ingots  A. Castaldini, A. Cavallini, E. Gombia, R.	50 (1991) 480	Neutron transmutation doping of	
Mosca and L. Tarricone, Evaluation		GaP: optical studies	50 (1991) 245
,		•	,,

M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic		Heterostructures	
properties of Si/Ge superlattices and $Si_{1-x}Ge_x$ films from surface acoustic modes by Brillouin scattering	50 (1991) 303	H. Cerva, Transmission electron mi- croscopy of heteroepitaxial layer	
B. Holländer, S. Mantl, B. Stritzker, F. Schäffler, HJ. Herzog and E. Kasper, Strain and defect densities in Si/		structures I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semicon-	50 (1991) 19
Si <sub>1-x</sub> Ge <sub>x</sub> heterostructures investigated by ion scattering and X-ray diffrac- tion	50 (1991) 450	ductor surfaces and interfaces  B. Deveaud, Subpicosecond luminescence spectroscopy of heterostructures (Ex-	50 (1991) 34
Gold	20 (2522) 100	tended Abstract)  N. Herres, G. Bender and G. Neumann, Assessment of mismatched epitaxial	50 (1991) 63
C. Ghezzi, R. Mosca, A. Bosacchi, S. Franchi and E. Gombia, The influence		layers by X-ray rocking curve meas- urements and simulations Y. Gao, I. Ardelean, D. Renard, B. Rose	50 (1991) 97
of the DX center on the capacitance of Schottky barriers in n-type AlGaAs	50 (1991) 400	and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP inter-	50 (1001) 121
L. Roberts and G. Hughes, An investiga- tion of metal/GaAs(100) interfaces by deep level transient spectroscopy	50 (1991) 424	faces T.S. Horányi, P. Tüttö and G. Endrédi, Improved method for depth profiling	50 (1991) 131
Hall effect	(,	of multilayer structures  J.S. Rimmer, M. Missous and A.R. Peaker,  A new, fast method for the computer	50 (1991) 143
G. Strasser, S. Dubois, M. Besson, E.		simulation of CV profiles in multi- layer structures	50 (1991) 149
Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity dis- tribution in n-GaAs layers by photo- conductivity and evelotron resonance		R.A.D. Mackenzie, J.A. Liddle and C.R.M. Grovenor, Ultrahigh resolu- tion characterisation of compound semiconductors using pulsed laser	
measurements D.I. Desnica, B. Šantić and U.V. Desnica,	50 (1991) 261	atom probe techniques  Z.M. Wang, J. Windscheif, D.J. As and W. Jantz, Ambient and low tempera-	50 (1991) 196
Time-evolution of low-temperature photoconductivity and Hall mobility in semi-insulating GaAs	50 (1991) 269	ture photoluminescence topography of GaAs substrates, epitaxial and im-	
B. Boudart, B. Prévot and C. Schwab, Free-carrier concentration in n-doped InP crystals determined by Raman		planted layers H.P. Zappe and G. Kaufel, Reactive-ion- etch damage in GaAs processing	50 (1991) 228
scattering measurements  A. Baraldi, C. Ghezzi, A. Parisini, A. Bosacchi and S. Franchi, Analysis of	50 (1991) 295	evaluated by a microwave absorption technique J.F. Donegan, J.P. Doran, R.P. Stanley, J.	50 (1991) 290
electron mobility versus temperature after photoexcitation in Si-doped Al <sub>x</sub> Ga <sub>1-x</sub> As	50 (1991) 405	Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in $Cd_xZn_{1-x}Te:ZnTe$	
R. Nipoti, D. Pocci, A. Cetronio and C. Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted GaAs by the differential sheet resistiv-		quantum wells: measurement of ho- mogeneous linewidths P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-	50 (1991) 321
ity and Hall effect technique  B. Mari, A. Segura and A. Chevy, Electrical properties of neutron-transmuta-	50 (1991) 410	grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films by means of non-destructive optical reflectometry	50 (1991) 330
tion-doped InSe D.A. Woolf, D.I. Westwood, M.A. Ander- son and R.H. Williams, The molecular beam epitaxial growth of GaAs(111)/	50 (1991) 415	C. Pickering, N.S. Garawal, D. Lance- field, J.P. Piel and R. Blunt, Non-de- structive characterisation of (Ga,In, Al,As,P)-based ternary multilayer	
Si(111): a variable growth temperature study	50 (1991) 445	structures using spectroscopic el- lipsometry	50 (1991) 346

D. Lee, S.J. Barnett, A.D. Pitt, M.R. Houlton and G.W. Smith, Characteri- zation of alloy composition in Ga <sub>1-x</sub> Al <sub>x</sub> As/GaAs structures: com- parison of photovoltage, X-ray, SIMS		S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter, E. Recknagel and ISOLDE Collabora- tion, Structural defect recovery in GaP after heavy ion implantation	50 (1991) 169
and RHEED techniques  B. Holländer, S. Mantl, B. Stritzker, F.	50 (1991) 428	Indium antimonide	
Schäffler, HJ. Herzog and E. Kasper, Strain and defect densities in Si/ Si <sub>1-x</sub> Ge <sub>x</sub> heterostructures investigated by ion scattering and X-ray diffrac- tion R. Schwarz, T. Fischer, P. Hanesch, T.	50 (1991) 450	<ul> <li>R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors</li> <li>A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Witt- huhn and ISOLDE Collaboration, Mi-</li> </ul>	50 (1991) 65
Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers	50 (1991) 456	croscopical studies at cadmium impurities in compound semiconductors  D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics of CdTe and CdMnTe layers grown	50 (1991) 165
Hydrogen		on InSb	50 (1991) 440
V.Kh. Kudoyarova, G.M. Gusinsky, L.A. Rassadin and I.V. Kudryavtsev, Hy-		Indium arsenide	
drogen depth profile measurement in $a-Si_{1-x}C_x$ :H films by elastic recoil detection	50 (1991) 173	R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors R. Zaus, M. Schuster, H. Göbel and JP.	50 (1991) 65
<ul> <li>J. Tatarkiewicz, A. Kozanecki, Z. Kaliński and K. Paprocki, Photoluminescence study of proton-implanted InP<sub>1-x</sub>As<sub>x</sub>:Yb</li> <li>M. Hage-Ali, B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Mi-</li> </ul>	50 (1991) 249	Reithmaier, Characterization of (In, Ga)As/GaAs strained-layer multiple quantum wells with high-resolution X-ray diffraction and computer simulations  A. Baurichter, M. Deicher, S. Deubler, D.	50 (1991) 92
croscopic defect level characterization of semi-insulating compound semicon- ductors by TSC and PICTS. Applica- tion to the effect of hydrogen in CdTe A.W.R. Leitch, Th. Prescha and M. Stutz- mann, Hydrogen passivation and re-	50 (1991) 377	Forkel, J. Meier, H. Wolf, W. Witt- huhn and ISOLDE Collaboration, Mi- croscopical studies at cadmium impur- ities in compound semiconductors B. Meyer, P. Omling and P. Emanuelsson,	50 (1991) 165
activation of shallow Zn acceptors in GaAs	50 (1991) 390	Landau oscillations in single quantum wells observed by microwave detec- tion	50 (1991) 420
Hydrogen sulphide		Indium phosphide	
G.M. O'Connor, C.J. McDonagh, F.G. Anderson, T.J. Glynn, G.P. Morgan, G.J. Hughes, L. Roberts and M.O. Henry, Raman characterization of	50 (1001) 212	I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces     C. Grattepain and A.M. Huber, Secondary ion mass spectrometry of	50 (1991) 34
passivated GaAs surfaces  Indium	50 (1991) 312	dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure	50 (1991) 42
R. Magerle, M. Deicher, U. Desnica, R. Keller, W. Pfeiffer, F. Pleiter, H. Skudlik and Th. Wichert, Defects in		R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors N. Herres, G. Bender and G. Neumann, Assessment of mismatched epitaxial	50 (1991) 65
CdS:In detected by perturbed angular correlation spectroscopy (PAC)	50 (1991) 159	layers by X-ray rocking curve meas- urements and simulations	50 (1991) 97

P. Ossart and E.V.K. Rao, Investigation of surface and sub-surface defects on polished InP substrates using Auger electron spectroscopy coupled to argon ion sputtering	50 (1991) 125	Monecke and E. Jahne, Characterization of III-V compounds by quasi- elastic electronic scattering of light C. Pickering, N.S. Garawal, D. Lance- field, J.P. Piel and R. Blunt, Non-de-	50 (1991) 300
<ul> <li>Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP interfaces</li> <li>J.G. Bauer, R. Treichler, T. Hillmer, J. Müller and G. Ebbinghaus, Optimization of Zn dopant profiles in a pin-di-</li> </ul>	50 (1991) 131	structive characterisation of (Ga,In, Al,As,P)-based ternary multilayer structures using spectroscopic ellipsometry  A. Dimoulas, A. Derekis, G. Kyriakidis and A. Christou, Alloy disorder effects in III-V ternaries studied by	50 (1991) 346
ode/FET by combination of depth profiling techniques: a SIMS, ECV and AES study W. Pfeiffer, M. Deicher, R. Keller, R.	50 (1991) 138	modulation spectroscopy H.W. Dinges, B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spec-	50 (1991) 353
Magerle, P. Pross, H. Skudlik, Th. Wichert, H. Wolf, D. Forkel, N. Moriya and R. Kalish, Characteriza-		troscopic ellipsometry  F. Mosel, A. Seidl, D. Hofmann and G.  Müller, Infrared absorption of n- and	50 (1991) 359
tion of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy A. Baurichter, M. Deicher, S. Deubler, D.	50 (1991) 154	<ul> <li>p-type Fe-doped InP and mapping of the Fe distribution</li> <li>B. Sartorius, M. Brandstättner and H. Venghaus, Two-wavelength transmis-</li> </ul>	50 (1991) 364
Forkel, J. Meier, H. Wolf, W. Wit- thuhn and ISOLDE Collaboration, Microscopical studies at cadmium im-		sion: a rapid and precise method for measuring the light absorption in semiconductors	50 (1991) 369
purities in compound semiconductors  B.L. Chen, M. Eckstein and HU.  Habermeier, Cathodoluminescence investigations of RIE-induced defects in	50 (1991) 165	J. Tardy, I. Thomas, P. Viktorovitch, M. Gendry, J.L. Perrossier, C. Santinelli, M.P. Besland, P. Louis and G. Post, Long-term stability of InP MIS de-	
InP R. Fornari, N. Tchandjou, P. Gall and J.M. Lussert, A study of structural	50 (1991) 191	vices  B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detec-	50 (1991) 383
properties of bulk double-doped InP by laser scattering tomography and photoetching	50 (1991) 207	tion	50 (1991) 420
H. L'Haridon, P.N. Favennec, R. Co- quille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial		Infrared spectroscopy  R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors	50 (1991) 65
investigation of an iron-doped indium phosphide ingot J. Tatarkiewicz, A. Kozanecki, Z. Kaliń- ski and K. Paprocki, Photolumines- cence study of proton-implanted	50 (1991) 237	V.Kh. Kudoyarova, G.M. Gusinsky, L.A. Rassadin and I.V. Kudryavtsev, Hydrogen depth profile measurement in a-Si <sub>1-x</sub> C <sub>x</sub> :H films by elastic recoil de-	30 (1991) 03
InP <sub>1-x</sub> As <sub>x</sub> :Yb G.M. Crean, P.A.F. Herbert, I. Little, W.M. Kelly, J.Y. Marzin, A. Izrael	50 (1991) 249	A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor	50 (1991) 173
and B. Jusserand, Investigation of re- active ion etch-induced damage in InP surfaces using a noncontact photo-	40 (4004) 207	electrical properties from the frequen- cy dependence of the dielectric con- stant: application to n-type ZnSe het-	50 (1001) 205
thermal radiometric probe  B. Boudart, B. Prévot and C. Schwab, Free-carrier concentration in n-doped InP crystals determined by Raman	50 (1991) 281	eroepitaxial thin films  F. Mosel, A. Seidl, D. Hofmann and G.  Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of	50 (1991) 285
scattering measurements  B.H. Bairamov, V.A. Voitenko, I.P. Ipatova, V.V. Toporov, G. Irmer, J.	50 (1991) 295	the Fe distribution  R. Schwarz, T. Fischer, P. Hanesch, T.  Muschik, J. Kolodzey, H. Cerva, H.L.	50 (1991) 364

Meyerheim and B.M.U. Scherzer,		S.C. Moss, J.F. Knudsen, R.C. Bowman,	
Limitations of interface sharpness in		Jr., P.M. Adams and D.D. Smith, Pi-	
a-Si:H/a-SiC:H multilayers	50 (1991) 456	cosecond transient photoreflectance	
M.R. Brozel, L. Breivik, D.J. Stirland,	50 (1331) 150	measurements of ion-implanted GaAs	50 (1991) 337
G.M. Williams and A.G. Cullis, Dislo-		M. Wagner, N. Winkler and H.D. Geiler,	50 (1),1) 551
cation density, infrared absorption and		Single-beam thermowave analysis of	
cathodoluminescence mapping of mi-		semiconductors	50 (1991) 373
		M. Hage-Ali, B. Yaacoub, S. Mergui, M.	30 (1331) 373
crostructure associated with disloca-	50 (1001) 475	Samimi, B. Biglari and P. Siffert, Mi-	
tion cells in semi-insulating LEC GaAs	50 (1991) 475		
		croscopic defect level characterization	
Ion bombardment		of semi-insulating compound semicon-	
		ductors by TSC and PICTS. Applica-	50 (1001) APP
WHI DE D. W. A. H. D. H		tion to the effect of hydrogen in CdTe	50 (1991) 377
H.W. Dinges, B. Kempf, H. Burkhard		R. Nipoti, D. Pocci, A. Cetronio and C.	
and R. Göbel, Determination of ion		Lanzieri, Carrier and mobility profile	
beam etching damage on InP by spec-		measurements in n-type ion-implanted	
troscopic ellipsometry	50 (1991) 359	GaAs by the differential sheet resistiv-	
		ity and Hall effect technique	50 (1991) 410
Ion implantation		V. Amarger, C. Dubon-Chevallier, A.C.	
10n implantation		Papadopoulo, B. Descouts and Y. Gao,	
		Correlated use of characterization	
J. Wagner, Raman spectroscopy for im-		techniques to optimize the Mg implan-	
purity characterization in III-V semi-		tation annealing for self-aligned HBT's	50 (1991) 462
conductors	50 (1991) 79	tation anneaming for sent anglises 115 1 s	20 (2772) 102
C. Frigeri, J.L. Weyher and M. De Potter,			
TEM study of the origin of the surface		Ion scattering	
microroughness in DSL photoetched			
Si-implanted GaAs wafers	50 (1991) 115	V.Kh. Kudoyarova, G.M. Gusinsky, L.A.	
W. Pfeiffer, M. Deicher, R. Keller, R.		Rassadin and I.V. Kudryavtsev, Hy-	
Magerle, P. Pross, H. Skudlik, Th.		drogen depth profile measurement in	
Wichert, H. Wolf, D. Forkel, N.		a- $Si_{1-x}C_x$ :H films by elastic recoil de-	
Moriya and R. Kalish, Characteriza-		$a - Si_{1-x}C_x$ . If thins by elastic recoil detection	50 (1991) 173
tion of Cd implanted and annealed			30 (1991) 173
GaAs and InP by perturbed angular		B. Holländer, S. Mantl, B. Stritzker, F.	
correlation (PAC) spectroscopy	50 (1991) 154	Schäffler, HJ. Herzog and E. Kasper,	
S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter,	30 (1991) 134	Strain and defect densities in Si/	
E. Recknagel and ISOLDE Collabora-		$Si_{1-x}Ge_x$ heterostructures investigated	
•		by ion scattering and X-ray diffrac-	
tion, Structural defect recovery in GaP	60 (1001) 160	tion	50 (1991) 450
after heavy ion implantation	50 (1991) 169	R. Schwarz, T. Fischer, P. Hanesch, T.	
Z.M. Wang, J. Windscheif, D.J. As and		Muschik, J. Kolodzey, H. Cerva, H.L.	
W. Jantz, Ambient and low tempera-		Meyerheim and B.M.U. Scherzer,	
ture photoluminescence topography of		Limitations of interface sharpness in	
GaAs substrates, epitaxial and im-		a-Si:H/a-SiC:H multilayers	50 (1991) 456
planted layers	50 (1991) 228		
H. L'Haridon, P.N. Favennec, R. Co-		T	
quille, M. Salvi, M. Gauneau, Y. Le		Iron	
Guillou, R. Callec and P. Gall, Spatial			
investigation of an iron-doped indium		H. L'Haridon, P.N. Favennec, R.	
phosphide ingot	50 (1991) 237	Coquille, M. Salvi, M. Gauneau, Y. Le	
J. Tatarkiewicz, A. Kozanecki, Z. Kaliń-	, ,	Guillou, R. Callec and P. Gall, Spatial	
ski and K. Paprocki, Photolumines-		investigation of an iron-doped indium	
cence study of proton-implanted		phosphide ingot	50 (1991) 237
InP <sub>1-x</sub> As <sub>x</sub> :Yb	50 (1991) 249	F. Mosel, A. Seidl, D. Hofmann and G.	()
A. Deneuville, C.H. Park, P. Ayyub, T.	00 (1771) 247	Müller, Infrared absorption of n- and	
Anderson, P. Lowen, K. Jones and		p-type Fe-doped InP and mapping of	
P.H. Holloway, O implantation in		the Fe distribution	50 (1991) 364
ZnSe: lattice distortion by Raman		B. Sartorius, M. Brandstättner and H.	20 (1771) 304
measurement	50 (1991) 308	Venghaus, Two-wavelength transmis-	
measurement	50 (1771) 500	· onguado, i wo-wavelength transmis-	

sion: a rapid and precise method for measuring the light absorption in		Luminescence	
semiconductors  L. Roberts and G. Hughes, An investigation of metal/GaAs(100) interfaces by	50 (1991) 369	B. Deveaud, Subpicosecond luminescence spectroscopy of heterostructures (Ex-	
deep level transient spectroscopy C. De las Heras, I.J. Ferrer and C. Sánchez, Comparison of pyrite thin films obtained from Fe and natural	50 (1991) 424	tended Abstract)  J. Schreiber, W. Hergert and S. Hildebrandt, Combined application of SEM-CL and SEM-EBIC for the investigation of compound semiconduc-	50 (1991) 63
pyrite powder	50 (1991) 505	tors A. Gustafsson, S. Nilsson and L. Samuel-	50 (1991) 181
Lanthanides		son, Intensity variations in the near- band-edge recombination of GaP epi-	
J. Tatarkiewicz, A. Kozanecki, Z. Kaliń- ski and K. Paprocki, Photolumines- cence study of proton-implanted		taxial layers, grown on (111) and (001) oriented substrates, as observed by	
InP <sub>1-x</sub> As <sub>x</sub> :Yb	50 (1991) 249	cathodoluminescence imaging  B.L. Chen, M. Eckstein and HU.  Habermeier, Cathodoluminescence in-	50 (1991) 186
Light scattering		vestigations of RIE-induced defects in InP	50 (1991) 191
R. Fornari, N. Tchandjou, P. Gall and J.M. Lussert, A study of structural properties of bulk double-doped InP by laser scattering tomography and		J.C. Fariñas and M.F. Barba, Inductively coupled plasma-atomic emission spectrometry (ICP-AES): an analyti- cal technique for the chemical char-	
photoetching B.H. Bairamov, V.A. Voitenko, I.P. Ipa-	50 (1991) 207	acterization of perovskite ceramic semiconductors	50 (1991) 202
tova, V.V. Toporov, G. Irmer, J. Monecke and E. Jahne, Characteriza-		A. Antolini and C. Lamberti, Computing errors in Fourier transform photo- luminescence	50 (1991) 212
tion of III-V compounds by quasi- elastic electronic scattering of light	50 (1991) 300	M. Baumgartner and K. Löhnert, Char-	30 (1991) 212
M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic		acterization of si-GaAs wafer quality by room-temperature photolumines- cence	50 (1991) 222
properties of Si/Ge superlattices and Si <sub>1-x</sub> Ge <sub>x</sub> films from surface acoustic modes by Brillouin scattering	50 (1991) 303	Z.M. Wang, J. Windscheif, D.J. As and W. Jantz, Ambient and low tempera-	30 (1991) 222
J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F.	()	ture photoluminescence topography of GaAs substrates, epitaxial and im-	
Austin, Resonant Rayleigh scattering from excitons in $Cd_xZn_{1-x}Te$ :ZnTe quantum wells: measurement of ho-	50 (1001) 201	planted layers  N. Ohnishi, Y. Makita, A. Yamada, H. Asakura and T. Matsumori, Effect of	50 (1991) 228
mogeneous linewidths  W. Kütt, G.C. Cho, M. Strahnen and H.  Kurz, Electro-optic sampling of	50 (1991) 321	substrate orientation on the defect-in- duced bound exciton emissions in GaAs grown by molecular beam epi-	
surface space-charge fields on III-V compounds	50 (1991) 325	taxy H. L'Haridon, P.N. Favennec, R. Co-	50 (1991) 233
S.C. Moss, J.F. Knudsen, R.C. Bowman, Jr., P.M. Adams and D.D. Smith, Pi- cosecond transient photoreflectance	,	quille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium	
measurements of ion-implanted GaAs  B. Sartorius, M. Brandstättner and H.  Venghaus, Two-wavelength transmission: a rapid and precise method for	50 (1991) 337	phosphide ingot  B.J. Heijmink Liesert, M. Godlewski, T.  Gregorkiewicz and C.A.J. Ammerlaan,  Neutron transmutation doping of	50 (1991) 237
measuring the light absorption in semiconductors	50 (1991) 369	GaP: optical studies  J. Tatarkiewicz, A. Kozanecki, Z. Kaliń-	50 (1991) 245
M. Wagner, N. Winkler and H.D. Geiler, Single-beam thermowave analysis of	50 (1991) 309	ski and K. Paprocki, Photolumines- cence study of proton-implanted	
semiconductors	50 (1991) 373	$InP_{1-x}As_x:Yb$	50 (1991) 249

T. Monteiro and E. Pereira, Complex for- mation in Mn-doped GaP samples	50 (1991) 253	Manganese	
<ul> <li>A. Zakrzewski and M. Godlewski, Three- center Auger effect and the quantum yield of the luminescence of ZnS-based phosphors</li> </ul>	50 (1991) 257	H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spec- troscopy of compound semiconduc-	
G.M. Crean, P.A.F. Herbert, I. Little, W.M. Kelly, J.Y. Marzin, A. Izrael	, , , , , , , , , , , , , , , , , , , ,	T. Monteiro and E. Pereira, Complex for- mation in Mn-doped GaP samples	50 (1991) 52 50 (1991) 253
and B. Jusserand, Investigation of re- active ion etch-induced damage in InP surfaces using a noncontact photo- thermal radiometric probe V. Amarger, C. Dubon-Chevallier, A.C. Papadopoulo, B. Descouts and Y. Gao, Correlated use of characterization	50 (1991) 281	S.J.C.H.M. van Gisbergen, M. Godlewski, T. Gregorkiewicz and C.A.J. Am- merlaan, Interstitial Mn as a new donor in GaP and GaAs: an EPR study	50 (1991) 273
techniques to optimize the Mg implan- tation annealing for self-aligned HBT's	50 (1991) 462	Mass spectroscopy	
M.R. Brozel, L. Breivik, D.J. Stirland, G.M. Williams and A.G. Cullis, Dislo- cation density, infrared absorption and cathodoluminescence mapping of mi-		R.A.D. Mackenzie, J.A. Liddle and C.R.M. Grovenor, Ultrahigh resolu- tion characterisation of compound	
crostructure associated with disloca- tion cells in semi-insulating LEC GaAs W. Jantz, R. Stibal, J. Windscheif and J. Wagner, Variation of material param-	50 (1991) 475	semiconductors using pulsed laser atom probe techniques	50 (1991) 196
eters along the growth direction of liquid encapsulated Czochralski grown		Mercury  A.M. Keir, S.J. Barnett, J. Giess, T.D.	
GaAs ingots  Magnesium	50 (1991) 480	Walsh and M.G. Astles, A combina- tion of high-resolution X-ray dif- fractometry and diffraction imaging techniques applied to the study of MOVPE-grown Cd <sub>x</sub> Hg <sub>1-x</sub> Te/CdTe on GaAs	50 (1991) 103
V. Amarger, C. Dubon-Chevallier, A.C. Papadopoulo, B. Descouts and Y. Gao, Correlated use of characterization techniques to optimize the Mg implan-		Metal - semiconductor interfaces	
tation annealing for self-aligned HBT's	50 (1991) 462	L. Roberts and G. Hughes, An investiga- tion of metal/GaAs(100) interfaces by deep level transient spectroscopy	50 (1991) 424
Magnetic measurements			
		Molecular beam epitaxy	
H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spec- troscopy of compound semiconduc- tors	50 (1991) 52	C.T. Foxon, Control of MBE, MOMBE and CBE growth using RHEED C. Grattepain and A.M. Huber, Sec-	50 (1991) 28
R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors B.J. Heijmink Liesert, M. Godlewski, T.	50 (1991) 65	ondary ion mass spectrometry of dopants and impurities in compound semiconductors: depth profiling of	
Gregorkiewicz and C.A.J. Ammerlaan, Neutron transmutation doping of GaP: optical studies	50 (1991) 245	homo- and heterostructure R. Zaus, M. Schuster, H. Göbel and JP. Reithmaier, Characterization of (In,	50 (1991) 42
B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detec-		Ga)As/GaAs strained-layer multiple quantum wells with high-resolution X-ray diffraction and computer simu-	
tion	50 (1991) 420	lations	50 (1991) 92

P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anter- roches and J. Massies, Interface		and single acceptor state of isolated $Ni_{Ga}$ in GaAs	50 (1991) 490
roughness of GaAs/AlAs super- lattices MBE-grown on vicinal surfaces N. Ohnishi, Y. Makita, A. Yamada, H.	50 (1991) 109	Noble gases	
Asakura and T. Matsumori, Effect of substrate orientation on the defect-in- duced bound exciton emissions in		S.C. Moss, J.F. Knudsen, R.C. Bowman, Jr., P.M. Adams and D.D. Smith, Pi- cosecond transient photoreflectance	
GaAs grown by molecular beam epi- taxy	50 (1991) 233	measurements of ion-implanted GaAs	50 (1991) 337
B. Jusserand and F. Mollot, Confined optical vibrations: a new probe for alloy disorder	50 (1991) 317	Optical properties	
C. Ghezzi, R. Mosca, A. Bosacchi, S. Franchi and E. Gombia, The influence of the DX center on the capacitance		H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spec- troscopy of compound semiconduc-	
of Schottky barriers in n-type AlGaAs C. Raisin, A. Rocher, G. Landa, R. Carles	50 (1991) 400	tors	50 (1991) 52
and L. Lassabatere, GaSb/GaAs het- eroepitaxy characterized as a stress- free system	50 (1991) 434	A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequen-	
D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between		cy dependence of the dielectric con- stant: application to n-type ZnSe het-	
electrical and structural characteristics of CdTe and CdMnTe layers grown		eroepitaxial thin films  J.F. Donegan, J.P. Doran, R.P. Stanley, J.  Hessetti, R.D. Feldman, and R.F.	50 (1991) 285
on InSb D.A. Woolf, D.I. Westwood, M.A. Anderson and R.H. Williams, The molecular	50 (1991) 440	Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in $Cd_xZn_{1-x}Te$ :ZnTe quantum wells: measurement of ho-	
beam epitaxial growth of GaAs(111)/ Si(111): a variable growth temperature study	50 (1991) 445	mogeneous linewidths W. Kütt, G.C. Cho, M. Strahnen and H.	50 (1991) 321
B. Holländer, S. Mantl, B. Stritzker, F. Schäffler, HJ. Herzog and E. Kasper, Strain and defect densities in Si/		Kurz, Electro-optic sampling of sur- face space-charge fields on III-V compounds	50 (1991) 325
Si <sub>1-x</sub> Ge <sub>x</sub> heterostructures investigated by ion scattering and X-ray diffrac-		P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE- grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films	
tion	50 (1991) 450	by means of non-destructive optical reflectometry	50 (1991) 330
MOS (metal-oxide-semiconductor) st	ructure	K. Jezierski, Z. Gumienny and J. Mis- iewicz, Reflectometry-aided surface	
G. Abstreiter, Micro-Raman spectroscopy for characterization of semiconductor		layer investigation  F. Mosel, A. Seidl, D. Hofmann and G.  Müller, Infrared absorption of n- and	50 (1991) 341
devices  J. Tardy, I. Thomas, P. Viktorovitch, M. Gendry, J.L. Perrossier, C. Santinelli,	50 (1991) 73	p-type Fe-doped InP and mapping of the Fe distribution	50 (1991) 364
M.P. Besland, P. Louis and G. Post, Long-term stability of InP MIS de-		S. Tüzemen and M.R. Brozel, An investi- gation of photo-quenching properties of LEC GaAs by using optical and	
vices	50 (1991) 383	electrical techniques  N. Hizem, G. Bremond, L. Mayet, M.	50 (1991) 395
Nickel		Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated	
N. Hizem, G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double		Ni <sub>Ga</sub> in GaAs  P. Roura, J.R. Morante, G. Bremond, T.  Benyattou, G. Guillot and W. Ulrici,	50 (1991) 490

Complete identification of the lated levels in GaP	e Ti-re- 50 (1991) 496	Oxygen	
Organometallic vapour depo	sition	Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP inter- faces	50 (1991) 131
C.T. Foxon, Control of MBE, M and CBE growth using RHEEI C. Grattepain and A.M. Hube	50 (1991) 28	A. Deneuville, C.H. Park, P. Ayyub, T. Anderson, P. Lowen, K. Jones and P.H. Holloway, O implantation in	30 (1331) 131
ondary ion mass spectrome dopants and impurities in con semiconductors: depth profil	etry of appound	ZnSe: lattice distortion by Raman measurement	50 (1991) 308
homo- and heterostructure	50 (1991) 42		
N. Herres, G. Bender and G. Net Assessment of mismatched el layers by X-ray rocking curve	pitaxial	Phosphorus	
urements and simulations  A.M. Keir, S.J. Barnett, J. Gies:  Walsh and M.G. Astles, A co tion of high-resolution X-ra	mbina- y dif-	HG. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Com- bined application of spreading-resis- tance and electron-microprobe depth	
fractometry and diffraction is techniques applied to the str MOVPE-grown Cd <sub>x</sub> Hg <sub>1-x</sub> Te <sub>j</sub>	ady of	profiling on GaAs:Zn and Si:P	50 (1991) 470
on GaAs	50 (1991) 103	Photoconductivity	
J.G. Bauer, R. Treichler, T. Hills Müller and G. Ebbinghaus, Op			
tion of Zn dopant profiles in a ode/FET by combination of profiling techniques: a SIMS	pin-di- depth ECV	R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors S.D. Baranovskii, Theoretical basis for the	50 (1991) 65
and AES study  A. Gustafsson, S. Nilsson and L. S son, Intensity variations in the		quantitative characterization of impur- ities in n-type III-V compound semi- conductors by photoelectromagnetic	
band-edge recombination of Ga taxial layers, grown on (111) and oriented substrates, as observe	aP epi- d (001) red by	spectroscopy G. Strasser, S. Dubois, M. Besson, E. Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity dis-	50 (1991) 218
z.M. Wang, J. Windscheif, D.J. A. W. Jantz, Ambient and low ter	mpera-	tribution in n-GaAs layers by photo- conductivity and cyclotron resonance	50 (1001) 261
ture photoluminescence topogra GaAs substrates, epitaxial an planted layers		measurements S. Usala, G.J. Adriaenssens, Ö. Öktü and M. Nesladek, Post-transit-time analy-	50 (1991) 261
P.L. Swart, B.M. Lacquet and R. T Physical characterization of OM grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer	havar, MVPE- films	sis of time-of-flight photocurrents D.I. Desnica, B. Šantić and U.V. Desnica, Time-evolution of low-temperature photoconductivity and Hall mobility	50 (1991) 265
by means of non-destructive reflectometry	50 (1991) 330	in semi-insulating GaAs  M. Hage-Ali, B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Mi-	50 (1991) 269
Oxides		croscopic defect level characterization of semi-insulating compound semicon- ductors by TSC and PICTS. Applica-	
J.C. Fariñas and M.F. Barba, Indu coupled plasma-atomic em spectrometry (ICP-AES): an a cal technique for the chemical acterization of perovskite co	ission nalyti- char-	tion to the effect of hydrogen in CdTe A. Baraldi, C. Ghezzi, A. Parisini, A. Bosacchi and S. Franchi, Analysis of electron mobility versus temperature after photoexcitation in Si-doped	50 (1991) 377
semiconductors	50 (1991) 202	$Al_xGa_{1-x}As$	50 (1991) 405

Photoelectron spectroscopy		ski and K. Paprocki, Photolumines- cence study of proton-implanted	
		InP <sub>1-x</sub> As <sub>x</sub> :Yb	50 (1991) 249
I.T. McGovern, Soft X-ray photoelectron		G.M. Crean, P.A.F. Herbert, I. Little,	30 (1991) 249
spectroscopy of compound semicon-		W.M. Kelly, J.Y. Marzin, A. Izrael	
ductor surfaces and interfaces	50 (1991) 34		
		and B. Jusserand, Investigation of re-	
D/		active ion etch-induced damage in InP	
Plasma processing		surfaces using a noncontact photo-	
		thermal radiometric probe	50 (1991) 281
A. Baurichter, M. Deicher, S. Deubler, D.		H.P. Zappe and G. Kaufel, Reactive-ion-	
Forkel, J. Meier, H. Wolf, W. Witt-		etch damage in GaAs processing	
huhn and ISOLDE Collaboration, Mi-		evaluated by a microwave absorption	
croscopical studies at cadmium impur-		technique	50 (1991) 290
ities in compound semiconductors	50 (1991) 165	H.W. Dinges, B. Kempf, H. Burkhard	()
	30 (1991) 103	and R. Göbel, Determination of ion	
B.L. Chen, M. Eckstein and HU.			
Habermeier, Cathodoluminescence in-		beam etching damage on InP by spec-	50 (1001) 250
vestigations of RIE-induced defects in		troscopic ellipsometry	50 (1991) 359
InP	50 (1991) 191		
G.M. Crean, P.A.F. Herbert, I. Little,		_	
W.M. Kelly, J.Y. Marzin, A. Izrael		Raman scattering	
and B. Jusserand, Investigation of re-			
active ion etch-induced damage in InP			
surfaces using a noncontact photo-		G. Abstreiter, Micro-Raman spectroscopy	
	60 (1001) 201	for characterization of semiconductor	
thermal radiometric probe	50 (1991) 281	devices	50 (1991) 73
H.P. Zappe and G. Kaufel, Reactive-ion-		J. Wagner, Raman spectroscopy for im-	
etch damage in GaAs processing		purity characterization in III-V semi-	
evaluated by a microwave absorption		conductors	50 (1991) 79
technique	50 (1991) 290	G.M. Crean, P.A.F. Herbert, I. Little,	30 (1))1)
A.W.R. Leitch, Th. Prescha and M. Stutz-			
mann, Hydrogen passivation and re-		W.M. Kelly, J.Y. Marzin, A. Izrael	
activation of shallow Zn acceptors in		and B. Jusserand, Investigation of re-	
GaAs	50 (1991) 390	active ion etch-induced damage in InP	
Gans	30 (1331) 330	surfaces using a noncontact photo-	
		thermal radiometric probe	50 (1991) 281
Quantum effects		B. Boudart, B. Prévot and C. Schwab,	
-		Free-carrier concentration in n-doped	
P. Davasud Submissessand luminessance		InP crystals determined by Raman	
B. Deveaud, Subpicosecond luminescence		scattering measurements	50 (1991) 295
spectroscopy of heterostructures (Ex-	## (## OO#)	B.H. Bairamov, V.A. Voitenko, I.P. Ipa-	00 (2772) 270
tended Abstract)	50 (1991) 63	tova, V.V. Toporov, G. Irmer, J.	
J.F. Donegan, J.P. Doran, R.P. Stanley, J.			
Hegarty, R.D. Feldman and R.F.		Monecke and E. Jahne, Characteriza-	
Austin, Resonant Rayleigh scattering		tion of III-V compounds by quasi-	
from excitons in Cd, Zn1-, Te: ZnTe		elastic electronic scattering of light	50 (1991) 300
quantum wells: measurement of ho-		A. Deneuville, C.H. Park, P. Ayyub, T.	
mogeneous linewidths	50 (1991) 321	Anderson, P. Lowen, K. Jones and	
B. Meyer, P. Omling and P. Emanuelsson,	30 (1771) 321	P.H. Holloway, O implantation in	
Landau oscillations in single quantum		ZnSe: lattice distortion by Raman	
		measurement	50 (1991) 308
wells observed by microwave detec-		G.M. O'Connor, C.J. McDonagh, F.G.	00 (2372) 000
tion	50 (1991) 420	Anderson, T.J. Glynn, G.P. Morgan,	
Radiation damage		G.J. Hughes, L. Roberts and M.O.	
Rudiation damage		Henry, Raman characterization of	
		passivated GaAs surfaces	50 (1991) 312
B.L. Chen, M. Eckstein and HU.		B. Jusserand and F. Mollot, Confined	
Habermeier, Cathodoluminescence in-		optical vibrations: a new probe for	
vestigations of RIE-induced defects in		alloy disorder	50 (1991) 317
InP	50 (1991) 191	S.C. Moss, J.F. Knudsen, R.C. Bowman,	
J. Tatarkiewicz, A. Kozanecki, Z. Kaliń-	,	Jr., P.M. Adams and D.D. Smith, Pi-	
		y a rarar a summar states are are transmiss, & A	

d described whatever		by means of non-destructive optical	
cosecond transient photoreflectance	50 (1991) 337	reflectometry	50 (1991) 330
measurements of ion-implanted GaAs	30 (1991) 337	D. Lee, S.J. Barnett, A.D. Pitt, M.R.	30 (1991) 330
C. Raisin, A. Rocher, G. Landa, R. Carles and L. Lassabatere, GaSb/GaAs het-		Houlton and G.W. Smith, Characteri-	
		zation of alloy composition in	
eroepitaxy characterized as a stress-	50 (1991) 434	$Ga_{1-x}Al_xAs/GaAs$ structures: com-	
free system	30 (1991) 434	parison of photovoltage, X-ray, SIMS	
		and RHEED techniques	50 (1991) 428
Reflection spectroscopy		V. Amarger, C. Dubon-Chevallier, A.C.	30 (1991) 420
		Papadopoulo, B. Descouts and Y. Gao,	
K. Jezierski, Z. Gumienny and J. Mis-		Correlated use of characterization	
iewicz, Reflectometry-aided surface		techniques to optimize the Mg implan-	
layer investigation	50 (1991) 341	tation annealing for self-aligned HBT's	50 (1991) 462
A. Dimoulas, A. Derekis, G. Kyriakidis	30 (1331) 341	P. Roura, J.R. Morante, G. Bremond, T.	30 (1991) 402
and A. Christou, Alloy disorder ef-		Benyattou, G. Guillot and W. Ulrici,	
fects in III-V ternaries studied by		Complete identification of the Ti-re-	
modulation spectroscopy	50 (1991) 353	lated levels in GaP	50 (1991) 496
modulation spectroscopy	30 (1991) 333	lated levels in GaP	30 (1991) 496
Schottky barrier		Semiconductor - semiconductor interfe	ices
C. Ghezzi, R. Mosca, A. Bosacchi, S.		P.F. Fewster, Multicrystal X-ray diffrac-	
Franchi and E. Gombia, The influence		tion of heteroepitaxial structures	50 (1991) 9
of the DX center on the capacitance		P. Auvray, A. Poudoulec, M. Baudet, B.	()
of Schottky barriers in n-type AlGaAs	50 (1991) 400	Guenais, A. Regreny, C. d'Anter-	
L. Roberts and G. Hughes, An investiga-		roches and J. Massies, Interface	
tion of metal/GaAs(100) interfaces by		roughness of GaAs/AlAs super-	
deep level transient spectroscopy	50 (1991) 424	lattices MBE-grown on vicinal surfaces	50 (1991) 109
L.J. Bredell, F.D. Auret, G. Myburg and		Y. Gao, I. Ardelean, D. Renard, B. Rose	()
W.O. Barnard, Electrical characteriza-		and Y. Jin, High-depth-resolution	
tion of argon-ion sputtered n-GaAs	50 (1991) 466	SIMS analysis for InGaAs/InP inter-	
		faces	50 (1991) 131
Secondary ion mass spectroscopy		J.S. Rimmer, M. Missous and A.R. Peaker,	(,
Secondary ton mass speem oscopy		A new, fast method for the computer	
		simulation of CV profiles in multi-	
C. Grattepain and A.M. Huber, Sec-		layer structures	50 (1991) 149
ondary ion mass spectrometry of		B. Jusserand and F. Mollot, Confined	20 (2222) 2.15
dopants and impurities in compound		optical vibrations: a new probe for	
semiconductors: depth profiling of	60 (1001) 40	alloy disorder	50 (1991) 317
homo- and heterostructure	50 (1991) 42	D.A. Woolf, D.I. Westwood, M.A. Ander-	30 (1),1)
Y. Gao, I. Ardelean, D. Renard, B. Rose		son and R.H. Williams, The molecular	
and Y. Jin, High-depth-resolution		beam epitaxial growth of GaAs(111)/	
SIMS analysis for InGaAs/InP inter-		Si(111): a variable growth temperature	
faces	50 (1991) 131	study	50 (1991) 445
J.G. Bauer, R. Treichler, T. Hillmer, J.		statey	50 (1))115
Müller and G. Ebbinghaus, Optimiza-			
tion of Zn dopant profiles in a pin-di-		Silicon	
ode/FET by combination of depth			
profiling techniques: a SIMS, ECV			
and AES study	50 (1991) 138	P.F. Fewster, Multicrystal X-ray diffrac-	E0 (1001)
H. L'Haridon, P.N. Favennec, R. Co-		tion of heteroepitaxial structures	50 (1991) 9
quille, M. Salvi, M. Gauneau, Y. Le		C. Grattepain and A.M. Huber, Sec-	
Guillou, R. Callec and P. Gall, Spatial		ondary ion mass spectrometry of	
investigation of an iron-doped indium		dopants and impurities in compound	
phosphide ingot	50 (1991) 237	semiconductors: depth profiling of	
P.L. Swart, B.M. Lacquet and R. Thavar,		homo- and heterostructure	50 (1991) 42
Physical characterization of OMVPE-		H.G. Grimmeiss and M. Kleverman,	
grown Al <sub>x</sub> Ga <sub>1-x</sub> As multi-layer films		Electrical and optical defect spec-	

troscopy of compound semiconduc- tors	50 (1991) 52	drogen depth profile measurement in a-Si <sub>1-x</sub> C <sub>x</sub> :H films by elastic recoil de-	
J. Wagner, Raman spectroscopy for im- purity characterization in III-V semi-		tection R. Schwarz, T. Fischer, P. Hanesch, T.	50 (1991) 173
conductors	50 (1991) 79	Muschik, J. Kolodzey, H. Cerva, H.L.	
C. Frigeri, J.L. Weyher and M. De Potter,		Meyerheim and B.M.U. Scherzer,	
TEM study of the origin of the surface		Limitations of interface sharpness in	
microroughness in DSL photoetched	50 (1001) 115	a-Si:H/a-SiC:H multilayers	50 (1991) 456
Si-implanted GaAs wafers	50 (1991) 115		
S. Usala, G.J. Adriaenssens, Ö. Öktü and		Silicon oxide	
M. Nesladek, Post-transit-time analy- sis of time-of-flight photocurrents	50 (1991) 265		
M. Mendik, M. Ospelt, H. von Känel and	30 (1991) 203	I.T. McGovern, Soft X-ray photoelectron	
P. Wachter, Determination of elastic		spectroscopy of compound semicon-	
properties of Si/Ge superlattices and		ductor surfaces and interfaces	50 (1991) 34
Si <sub>1-x</sub> Ge <sub>x</sub> films from surface acoustic		G. Abstreiter, Micro-Raman spectroscopy	
modes by Brillouin scattering	50 (1991) 303	for characterization of semiconductor	
A. Baraldi, C. Ghezzi, A. Parisini, A.		devices	50 (1991) 73
Bosacchi and S. Franchi, Analysis of			
electron mobility versus temperature		Sputtering	
after photoexcitation in Si-doped			
$Al_xGa_{1-x}As$	50 (1991) 405	L.J. Bredell, F.D. Auret, G. Myburg and	
R. Nipoti, D. Pocci, A. Cetronio and C.		W.O. Barnard, Electrical characteriza-	
Lanzieri, Carrier and mobility profile		tion of argon-ion sputtered n-GaAs	50 (1991) 466
measurements in n-type ion-implanted			
GaAs by the differential sheet resistiv-	50 (1991) 410	Sulphides	
ity and Hall effect technique D.A. Woolf, D.I. Westwood, M.A. Ander-	30 (1991) 410		
son and R.H. Williams, The molecular		C. Levade, J.J. Couderc, G. Vander-	
beam epitaxial growth of $GaAs(\overline{111})$		schaeve, D. Caillard and A. Couret,	
Si(111): a variable growth temperature		TEM in-situ observation of recombi-	
study	50 (1991) 445	nation-enhanced mobility of disloca-	
B. Holländer, S. Mantl, B. Stritzker, F.		tions in II-VI compounds	50 (1991) 119
Schäffler, HJ. Herzog and E. Kasper,		A. Zakrzewski and M. Godlewski, Three-	
Strain and defect densities in Si/		center Auger effect and the quantum	
Si <sub>1-x</sub> Ge <sub>x</sub> heterostructures investigated		yield of the luminescence of ZnS-based	
by ion scattering and X-ray diffrac-		phosphors	50 (1991) 257
tion	50 (1991) 450	C. De las Heras, I.J. Ferrer and C.	
R. Schwarz, T. Fischer, P. Hanesch, T.		Sánchez, Comparison of pyrite thin	
Muschik, J. Kolodzey, H. Cerva, H.L.		films obtained from Fe and natural	ED (1001) EDE
Meyerheim and B.M.U. Scherzer,		pyrite powder	50 (1991) 505
Limitations of interface sharpness in	60 (1001) 466		
a-Si:H/a-SiC:H multilayers	50 (1991) 456	Superlattices	
HG. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Com-			
bined application of spreading-resis-		P.F. Fewster, Multicrystal X-ray diffrac-	
tance and electron-microprobe depth		tion of heteroepitaxial structures	50 (1991) 9
profiling on GaAs:Zn and Si:P	50 (1991) 470	C. Grattepain and A.M. Huber, Sec-	
A. Castaldini, A. Cavallini, E. Gombia, R.	00 (2002)	ondary ion mass spectrometry of	
Mosca and L. Tarricone, Evaluation		dopants and impurities in compound	
of the diffusion length of minority car-		semiconductors: depth profiling of	50 (1991) 42
riers in bulk GaAs	50 (1991) 485	homo- and heterostructure	30 (1991) 42
		J.H.C. Hogg, D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial	
Silicon carbide		multilayer structures using X-ray	
		simulation techniques	50 (1991) 87
V.Kh. Kudoyarova, G.M. Gusinsky, L.A.		R. Zaus, M. Schuster, H. Göbel and JP.	()
Rassadin and I.V. Kudryavtsev, Hy-		Reithmaier, Characterization of (In,	

Ga)As/GaAs strained-layer multiple quantum wells with high-resolution X-ray diffraction and computer simu-		C. Frigeri, J.L. Weyher and M. De Potter, TEM study of the origin of the surface microroughness in DSL photoetched	
lations P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anterroches and J. Massies, Interface	50 (1991) 92	Si-implanted GaAs wafers R.A.D. Mackenzie, J.A. Liddle and C.R.M. Grovenor, Ultrahigh resolu- tion characterisation of compound	50 (1991) 115
roughness of GaAs/AlAs super- lattices MBE-grown on vicinal surfaces M. Mendik, M. Ospelt, H. von Känel and	50 (1991) 109	semiconductors using pulsed laser atom probe techniques	50 (1991) 196
P. Wachter, Determination of elastic properties of Si/Ge superlattices and $Si_{1-x}Ge_x$ films from surface acoustic		Tin	
modes by Brillouin scattering  B. Jusserand and F. Mollot, Confined optical vibrations: a new probe for alloy disorder	50 (1991) 303 50 (1991) 317	B. Mari, A. Segura and A. Chevy, Electri- cal properties of neutron-transmuta- tion-doped InSe	50 (1991) 415
andy disorder	00 (2332) 021	Titanium	
Surface and interface states		1 ttumum	
L. Roberts and G. Hughes, An investiga-		P. Roura, J.R. Morante, G. Bremond, T. Benyattou, G. Guillot and W. Ulrici, Complete identification of the Ti-re-	
tion of metal/GaAs(100) interfaces by deep level transient spectroscopy	50 (1991) 424	lated levels in GaP	50 (1991) 496
Surface phonons and adsorbate vibrate	tions	X-ray diffraction	
M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic properties of Si/Ge superlattices and Si <sub>1-x</sub> Ge <sub>x</sub> films from surface acoustic modes by Brillouin scattering	50 (1991) 303	J. Matsui, Study of strain variation in LEC-grown GaAs bulk crystals by synchrotron radiation X-ray topogra- phy P.F. Fewster, Multicrystal X-ray diffrac-	50 (1991) 1
Surface photovoltage		tion of heteroepitaxial structures J.H.C. Hogg, D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial	50 (1991) 9
D. Lee, S.J. Barnett, A.D. Pitt, M.R. Houlton and G.W. Smith, Characterization of alloy composition in Ga <sub>1-x</sub> Al <sub>x</sub> As/GaAs structures: comparison of photovoltage, X-ray, SIMS		multilayer structures using X-ray simulation techniques R. Zaus, M. Schuster, H. Göbel and JP. Reithmaier, Characterization of (In, Ga)As/GaAs strained-layer multiple quantum wells with high-resolution	50 (1991) 87
and RHEED techniques  A. Castaldini, A. Cavallini, E. Gombia, R.	50 (1991) 428	X-ray diffraction and computer simulations	50 (1991) 92
Mosca and L. Tarricone, Evaluation of the diffusion length of minority car- riers in bulk GaAs	50 (1991) 485	N. Herres, G. Bender and G. Neumann, Assessment of mismatched epitaxial layers by X-ray rocking curve meas-	
Surface roughness		urements and simulations A.M. Keir, S.J. Barnett, J. Giess, T.D. Walsh and M.G. Astles, A combina-	50 (1991) 97
-		tion of high-resolution X-ray dif-	
<ul> <li>P.F. Fewster, Multicrystal X-ray diffraction of heteroepitaxial structures</li> <li>P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anter-</li> </ul>	50 (1991) 9	fractometry and diffraction imaging techniques applied to the study of MOVPE-grown Cd <sub>x</sub> Hg <sub>1-x</sub> Te/CdTe on GaAs	50 (1991) 103
roches and J. Massies, Interface roughness of GaAs/AlAs super- lattices MBE-grown on vicinal surfaces	50 (1991) 109	P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anterroches and J. Massies, Interface	

roughness of GaAs/AlAs super- lattices MBE-grown on vicinal surfaces P.L. Swart, B.M. Lacquet and R. Thavar,	50 (1991) 109	$Si_{1-x}Ge_x$ heterostructures investigated by ion scattering and X-ray diffrac-	50 (1991) 450
Physical characterization of OMVPE- grown $Al_xGa_{1-x}As$ multi-layer films		R. Schwarz, T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L.	30 (1991) 430
by means of non-destructive optical reflectometry	50 (1991) 330	Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in	
S.C. Moss, J.F. Knudsen, R.C. Bowman,	30 (1771) 330	a-Si:H/a-SiC:H multilayers	50 (1991) 456
Jr., P.M. Adams and D.D. Smith, Pi-		C. De las Heras, I.J. Ferrer and C.	
cosecond transient photoreflectance measurements of ion-implanted GaAs	50 (1991) 337	Sánchez, Comparison of pyrite thin films obtained from Fe and natural	
D. Lee, S.J. Barnett, A.D. Pitt, M.R.	30 (1991) 337	pyrite powder	50 (1991) 505
Houlton and G.W. Smith, Characteri-		F)	()
zation of alloy composition in		Zinc	
$Ga_{1-x}Al_xAs/GaAs$ structures: comparison of photovoltage, X-ray, SIMS		J.G. Bauer, R. Treichler, T. Hillmer, J.	
and RHEED techniques	50 (1991) 428	Müller and G. Ebbinghaus, Optimiza-	
D. Ashenford, J.H.C. Hogg, B. Lunn and		tion of Zn dopant profiles in a pin-di-	
C.G. Scott, The relationship between		ode/FET by combination of depth	
electrical and structural characteristics of CdTe and CdMnTe layers grown		profiling techniques: a SIMS, ECV and AES study	50 (1991) 138
on InSb	50 (1991) 440	A.W.R. Leitch, Th. Prescha and M. Stutz-	30 (1331) 130
D.A. Woolf, D.I. Westwood, M.A. Ander-		mann, Hydrogen passivation and re-	
son and R.H. Williams, The molecular		activation of shallow Zn acceptors in GaAs	50 (1991) 390
beam epitaxial growth of GaAs(111)/ Si(111): a variable growth temperature		HG. Hettwer, W. Lerch, B. Lentfort,	30 (1991) 390
study	50 (1991) 445	N.A. Stolwijk and H. Mehrer, Com-	
B. Holländer, S. Mantl, B. Stritzker, F.		bined application of spreading-resis-	
Schäffler, HJ. Herzog and E. Kasper, Strain and defect densities in Si/		tance and electron-microprobe depth profiling on GaAs:Zn and Si:P	50 (1991) 470
Strain and detect densities in Si/		proming on GaAs. Zil and St. F	30 (1991) 4/0